

Supplementary Information

Solution-Processable Ni₃(HITP)₂/MXene Heterostructures for ppb-Level Gas Detection

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Materials

The chemicals for the synthesis of MOF suspensions were purchased from commercial suppliers, including nickel nitrate hexahydrate ($\text{Ni}(\text{NO}_3)_2 \cdot 6\text{H}_2\text{O}$, purity > 98%, Sigma-Aldrich), 2,3,6,7,10,11-hexahydroxytriphenylene (HITP, purity > 97%, Macklin), multilayered MXene nanosheet dispersion in ethanol (Nb_2C , purity > 99%, $5 \text{ g} \cdot \text{L}^{-1}$, Xixi Technology Co., Ltd.), ammonia solution (purity \approx 30%, Sigma-Aldrich), and anhydrous ethanol (EtOH, purity > 99.8%, Sigma-Aldrich). All the chemicals were used without further purification.

Methods

Synthesis of $\text{Ni}_3(\text{HITP})_2/\text{MXene}$ Heterostructures and Powder

The synthesis process of $\text{Ni}_3(\text{HITP})_2/\text{MXene}$ suspensions involved several steps. Firstly, Nickel nitrate hexahydrate ($\text{Ni}(\text{NO}_3)_2 \cdot 6\text{H}_2\text{O}$, 50 mg) was dissolved in a mixed solution of anhydrous ethanol (25 mL) and concentrated ammonia solution (2 mL, 30%), and dissolving 2,3,6,7,10,11-hexaaminotriphenyl (HITP, 33 mg) in anhydrous ethanol (25 mL), then mixing it and adding the multi-layer MXene (Nb_2C) nanosheet dispersion (5 mL) to it. The synthesis took place at a temperature of 65 °C for a duration of 5 hours. The solution was composed of anhydrous ethanol (50 mL) and concentrated ammonia solution (2 mL, 30%). After synthesis, the resulting suspensions had a viscous consistency to remove impurities and unwanted by-products, the suspensions were rinsed five times with fresh anhydrous ethanol using a centrifuge operating at a speed of 8000 rpm. Subsequently, the rinsed suspensions were soaked in fresh anhydrous ethanol overnight. To further purify the suspensions, they were soaked in absolute ethanol for an additional two days, with the solvent being renewed periodically. Finally, the washed $\text{Ni}_3(\text{HITP})_2/\text{MXene}$ suspension was subjected to vacuum drying at a temperature of 150 °C. This drying process resulted in the formation of $\text{Ni}_3(\text{HITP})_2/\text{MXene}$ powder. Additionally, the reaction container we used was a 100 ml hydrothermal reaction

vessel with an inner lining made of polytetrafluoroethylene (PTFE). This container is characterized by its resistance to strong acids and bases, high temperature, and airtightness.

Synthesis of Ni₃(HITP)₂ Suspensions and Powder

Ni₃(HITP)₂ suspensions were synthesized by reacting a mixture solution containing HITP (33 mg) and Ni(NO₃)₂·6H₂O (50 mg) at 65 °C for 5 hours. The solution was composed of anhydrous ethanol (50 mL) and concentrated ammonia solution (2 mL, 30%). The resulting suspension was washed five times with fresh anhydrous ethanol using a centrifuge at a speed of 8000 rpm, then soaked in fresh anhydrous ethanol overnight. The washed Ni₃(HITP)₂ suspension was dried under vacuum at 150 °C to obtain Ni₃(HITP)₂ powder.

Fabrication of Ni₃(HITP)₂/MXene and MXene Monodispersed nanosheets

A suspension of alcoholic Ni₃(HITP)₂/MXene or MXene, with a concentration of 0.5 g L⁻¹ and a volume of 20 μL, was meticulously applied onto a pristine silicon wafer or a copper mesh using the drop-casting. Subsequently, the sample was subjected to a drying process at a temperature of 80 °C for a duration of 20 minutes. This drying step effectively removed a significant portion of the solvent present in the sample. Following the initial drying process, the sample underwent a slow drying process under vacuum conditions for a period of one day. This extended drying period allowed for the gradual removal of any remaining solvent, resulting in the formation of uniformly monodispersed nanosheets of Ni₃(HITP)₂/MXene and MXene. These can be used for SEM and TEM characterizations. The slow drying process under vacuum conditions is essential for promoting the uniform distribution and arrangement of the nanosheets, which contributes to their overall quality and monodispersity.

Fabrication of Ni₃(HITP)₂/MXene Films

Ni₃(HITP)₂/MXene films on Si substrates were fabricated just via drop-casting. Typically, Si substrates were thoroughly rinsed by absolute ethanol twice under fierce stirring with each

circle for 10 min, afterward dried at 80 °C under ambient pressure. A certain volume of Ni₃(HITP)₂/MXene ethanol suspension was then captured by pipette and vertically dropped onto Si surfaces. Ni₃(HITP)₂/MXene films can thus be formed along with the vaporization of ethanol. For the film fabricated on polyvinylidene fluoride (PVDF) substrate: the PVDF substrate was blew with N₂ gas gun to remove surface dust. The pre-treated PVDF substrate was placed on an automatic film coater. Viscous Ni₃(HITP)₂/MXene alcoholic suspension with a concentration of 5 g·L⁻¹ and a volume of 8 mL was dropped by pipette onto the PVDF substrate. Afterward, doctor-blading with a set height of 10 μm was performed at a speed of 1.0 cm·s⁻¹ on the PVDF substrate. For the chip-level integration of Ni₃(HITP)₂/MXene films, chips were thoroughly cleaned twice by anhydrous ethanol without stirring. Each rinsing circle was kept for 10 min, and the chips were dried at 80 °C under ambient pressure. Relevant Ni₃(HITP)₂/MXene suspensions in ethanol with the same solid concentration (0.8 g·L⁻¹) and volume (20 μL) were drop-casted onto the chips. Drying for all kinds of films was conducted at the ambient condition to fully vaporize the solvent, affording flat films.

Design and Fabrication of sensors

Platinum (Pt) interdigitated electrodes (IDEs) were produced and structured on silicon (Si) (100) wafers utilizing established cleanroom techniques, as documented in a previous publication¹. The fabrication process involved precise patterning of Pt material on the Si wafers to create the interdigitated electrode configuration. Furthermore, a Pt micro-hotplate was integrated beneath the top IDEs, serving as a micro-heater. This micro-heater had the potential to activate the metal-organic framework (MOF) films in-situ. After the fabrication process, the wafers were diced into individual chips. These chips were then soldered onto printed circuit boards (PCB) to establish electrical connections. The wire coupling process, which involved connecting the IDEs to the relevant circuitry, was carried out subsequent to the soldering of the chips.

Theoretical Calculations

Density functional theory (DFT) calculations were performed using the generalized gradient approximation (GGA) for the exchange-correlation potential, the projector augmented wave (PAW) method²⁻³, and a plane-wave basis set as implemented in the Viennaab initio simulation package (VASP)⁴⁻⁵. Van der Waals interaction were considered at the van der Waals density functional (vdW-DF) level with the optB86b functional (optB86b-vdW)⁶. The heterostructure consisted of a monolayer Ni₃(HITP)₂ and a 7 × 7 bilayer Nb₂C superlattice with a vacuum layer of approximately 35 Å, and the lattice mismatch between Ni₃(HITP)₂ and the MXene is less than 0.7%. In structural relaxations, all atoms were fully relaxed until the residual force on every atom was less than 0.05 eV·Å⁻¹. The kinetic energy cut off for the plane-wave basis was set to 500 eV. The adsorption energy was derived as follow: $E_{\text{ads}} = E_{\text{molecule} + \text{substrate}} - E_{\text{substrate}} - E_{\text{molecule}}$, where E_{ads} is the adsorption energy, $E_{\text{molecule} + \text{substrate}}$ is the total energy of adsorption geometry. $E_{\text{substrate}}$ and E_{molecule} is the energy of an individual substrate and the isolated molecule, respectively.

Gas Sensing Tests

The gas sensing performance of the sensors based on Ni₃(HITP)₂/MXene films was evaluated by measuring the resistance change before and after gas adsorption. During the measurement process, the chip was placed in a custom chamber with stretchable metal contacts. Before data acquisition, the chamber was purged with nitrogen (N₂) for 15 minutes to stabilize the baseline resistance. N₂ was also used as a diluent to reach the target concentration and for sensor regeneration. The flow rate of all gases was kept constant at 100 sccm. A simplified scheme of the experimental set-up is available in the Figure S19.

The response was defined as the value obtained by sensor electrically-transduced signal changes in detected gas and purging gas (Δ (saturated signal change in gaseous

analytes)/(signal baseline in purging gas)). For example, the response of Ni₃(HITP)₂/MXene and Ni₃(HITP)₂ resistive sensor toward EtOH in air can be obtained by Eq. S1,

$$\text{Response} = \frac{|\Delta R|}{R_{air}} = \frac{|R_{gas} - R_{air}|}{R_{air}} \quad \text{Eq. S1}$$

In order to determine the detection limit of the Ni₃(HITP)₂/MXene and Ni₃(HITP)₂ resistive sensor toward EtOH and NH₃, the standard deviation (SD) of the relevant response was calculated according to Eq. S2⁷,

$$\text{SD} = \sqrt{\frac{\sum_{i=1}^n (y_a - y_{a^*})^2}{n-2}} \quad \text{Eq. S2}$$

in which y_a and y_{a^*} denote the experimental and fitted responses, respectively, under the same EtOH or NH₃ concentration; n stands for the total points tested. The derived SD was then multiplied by a factor of 3, which was assigned to the relevant response upon exposure to the limit of detection of EtOH or NH₃. As such, the limit of detection can be derived by mapping the fitted curve as shown in Figure 2 (e) and 2 (f), i.e., EtOH (5 ppb) and NH₃ (250 ppb).

Characterizations

Fourier-transform infrared (FTIR) patterns were obtained by a Nicolet iS50 FTIR spectrometer. XPS spectrum obtained by ESCALAB Xi⁺ X-ray photoelectron spectroscopy. Microstructural characterizations of Ni₃(HITP)₂/MXene nanosheets and relevant films, were characterized by scanning electron microscopy (SEM, SU8230) and X-ray diffractometer (XRD, Bruker) equipped with Cu K α radiation ($\lambda = 1.5406 \text{ \AA}$) under a Bragg-Brentano geometry with a step size of 0.02° and a scan speed of $0.5^\circ \cdot \text{min}^{-1}$. Two-dimensional (2D) grazing-incidence wide-angle X-ray scattering (GIWAXS) measurements were performed on Nanoinxider (Xenocs) with Cu K α radiation as the source at an incidence angle of 0.2° . Transmission electron microscopy (TEM) imaging was conducted via a JEOL TEM (JEM-

2100). High angle annular dark field (HAADF)-STEM imaging was performed by a JEM-ARM200F (JEOL) microscope equipped with an ASCOR aberration corrector and a cold-field emission gun, operated at 200 kV. Focused ion beam coupled transmission electron microscopy (FIB-TEM) imaging was performed via a JEOL TEM coupled with a Ga ion beam. AFM tapping mode was used for the morphology and height analysis of Ni₃(HITP)₂/MXene and MXene nanosheets or films at room temperature. The measurements were performed on a Bruker Edge instrument with scanning rate at 0.7 Hz. N₂ sorption isotherms were collected under 77 K using a Micromeritics ASAP 2460 surface area and pore size analyzer. Measuring the conductivity of Ni₃(HITP)₂/MXene and MXene powder using the standard four electrode method, the set pressure ranges from 2.0 to 30.0 MPa.

Additional results

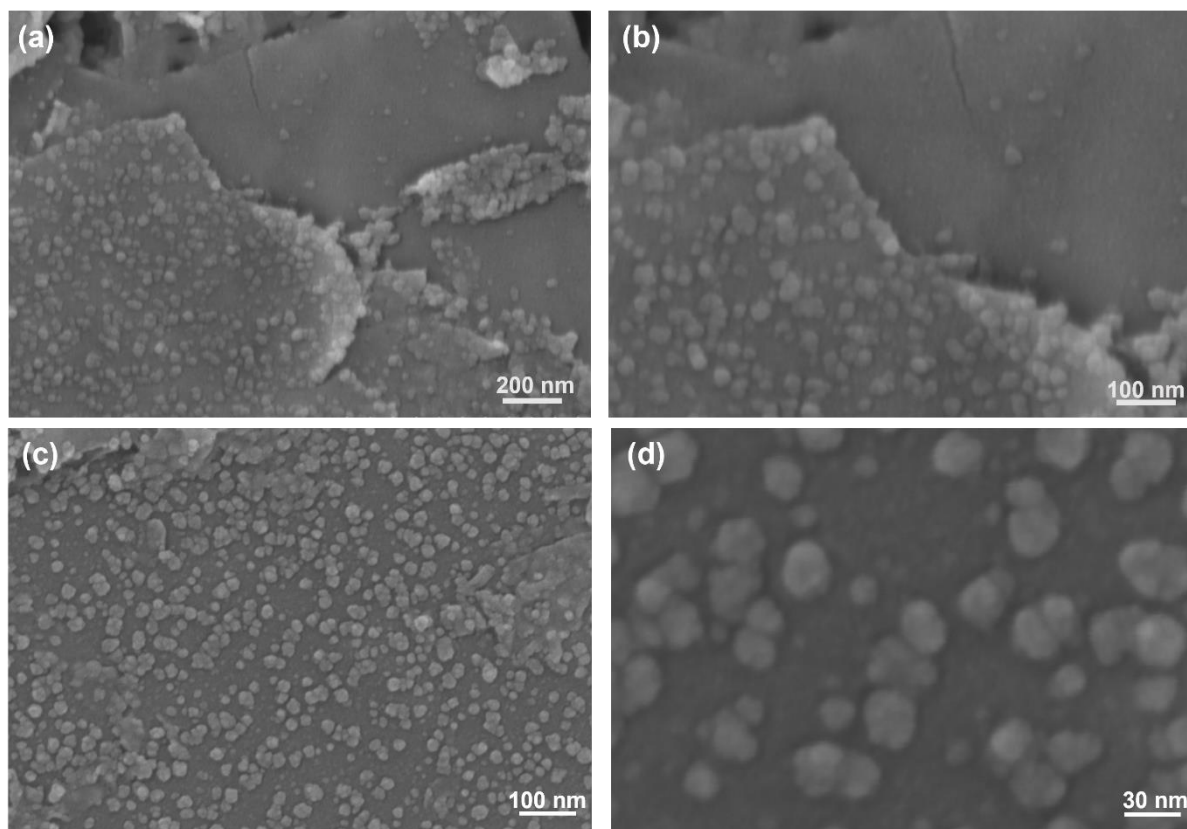


Figure S1. (a-b) SEM images of the $\text{Ni}_3(\text{HITP})_2/\text{MXene}$ heterostructure on a silicon substrate.

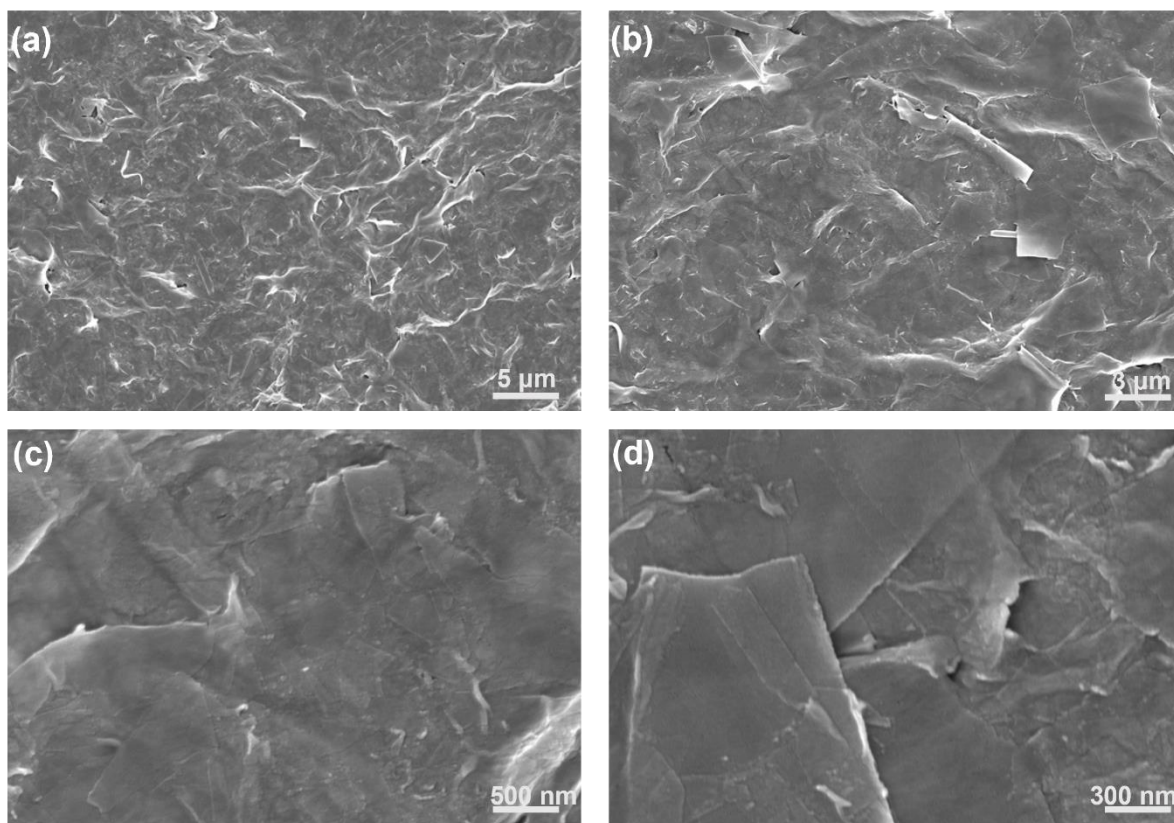


Figure S2. (a-d) SEM images of the MXene nanosheets on a silicon substrate.

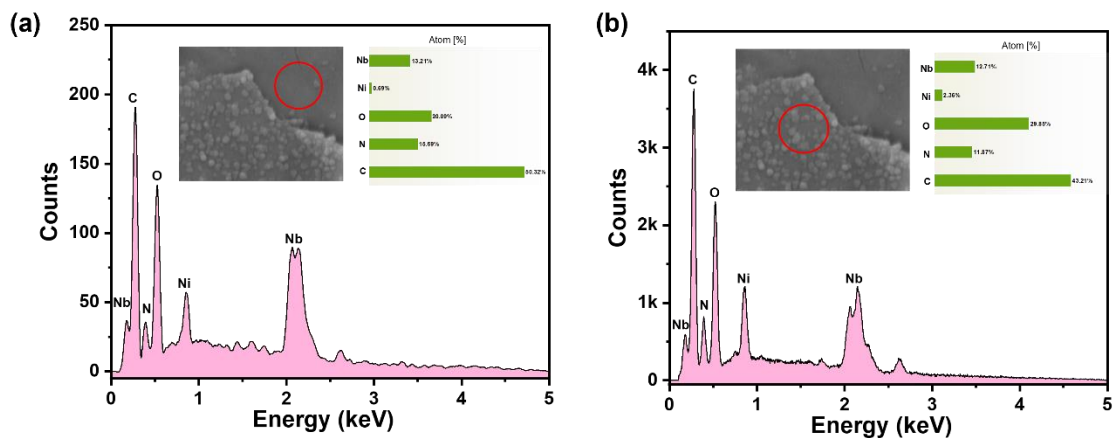


Figure S3. (a-b) Elemental composition and distribution on both sides of edge of the $\text{Ni}_3(\text{HITP})_2/\text{MXene}$ heterostructure: (a) MXene. (b) $\text{Ni}_3(\text{HITP})_2/\text{MXene}$.

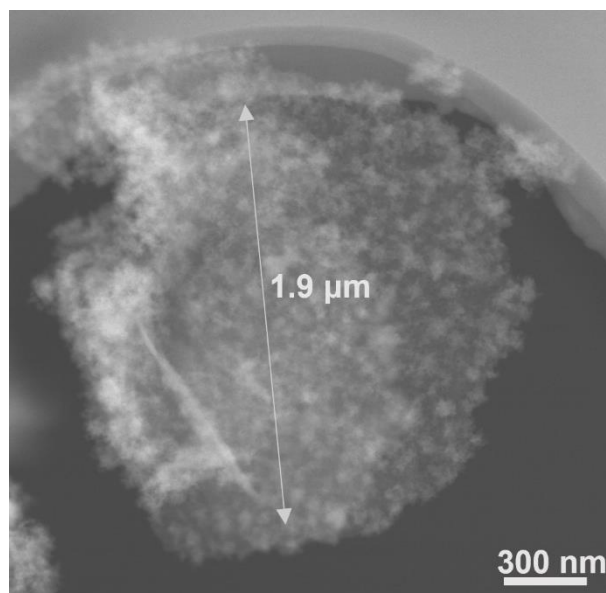


Figure S4. Low-magnification TEM image of the well-dispersed $\text{Ni}_3(\text{HITP})_2/\text{MXene}$ nanosheets.

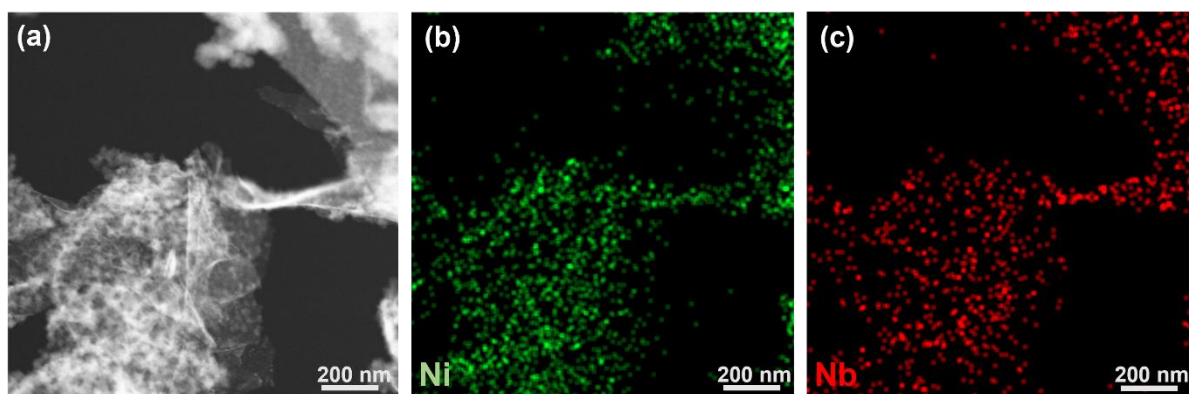


Figure S5. (a) Low-magnification TEM image of well-dispersed $\text{Ni}_3(\text{HITP})_2/\text{MXene}$ nanosheets. (b-c) The elemental Ni and Nb mapping images of the $\text{Ni}_3(\text{HITP})_2/\text{MXene}$ nanosheets.

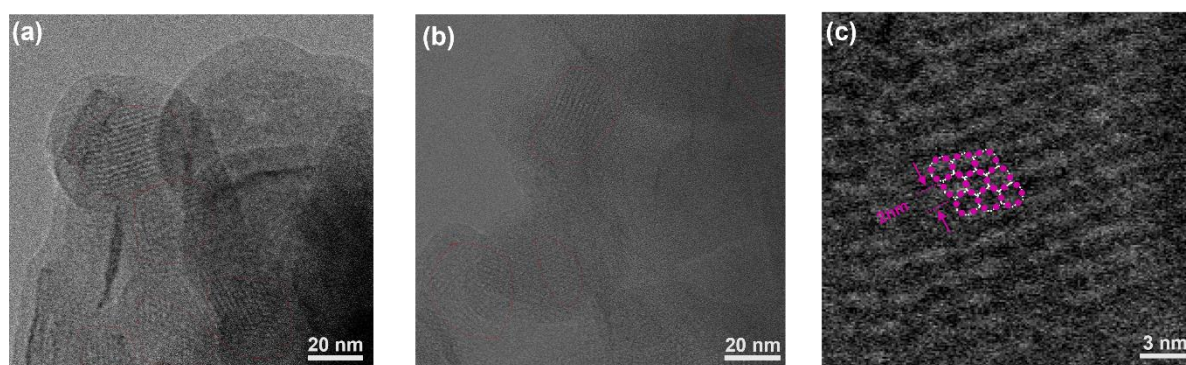


Figure S6. (a-c) STEM images of the $\text{Ni}_3(\text{HITP})_2/\text{MXene}$ nanosheet. Inset depicts the schematic illustration of the $\text{Ni}_3(\text{HITP})_2$ framework viewed from *c*-direction.

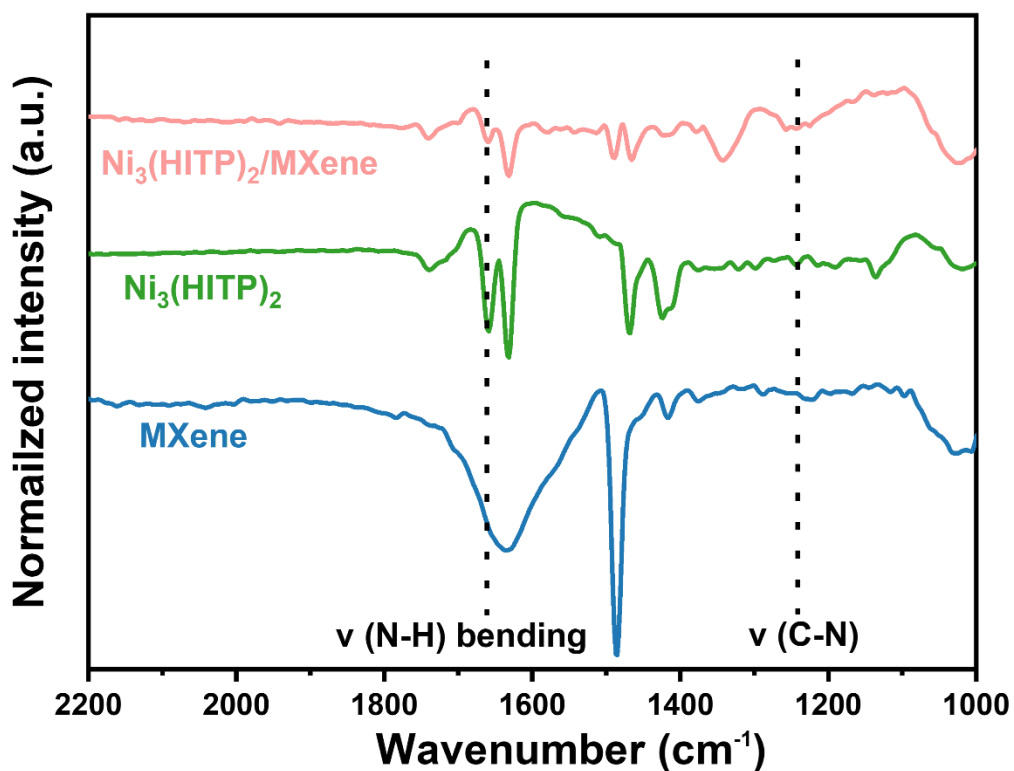


Figure S7. FTIR spectra comparison of the Ni₃(HITP)₂/MXene structure and MXene structure.

Note: Regarding the infrared spectra of the Ni₃(HITP)₂/MXene structure, in addition to the characteristic peaks attributed to MXene, we also observed peaks appearing in the infrared shift range of 1000-1600 cm⁻¹, which can be attributed to the vibration of C-C bonds in the HITP linker of Ni₃(HITP)₂, indicating the successful formation of the Ni₃(HITP)₂/MXene structure (Figure S1).

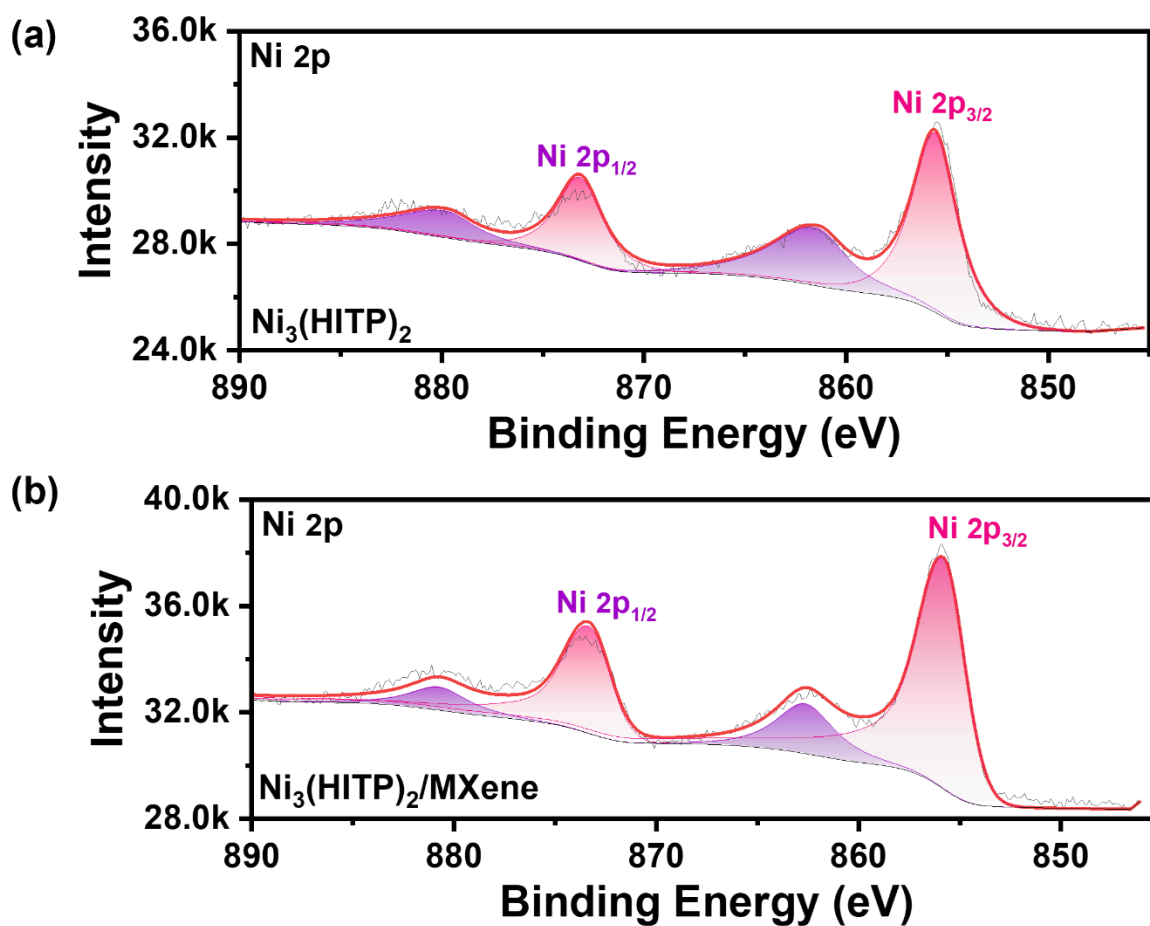


Figure S8. (a-b) Ni 2p X-ray photoelectron spectroscopy (XPS) spectra of (a) $\text{Ni}_3(\text{HITP})_2$ powder and (b) $\text{Ni}_3(\text{HITP})_2/\text{MXene}$ structure.

Note: The chemical environment of Ni in the $\text{Ni}_3(\text{HITP})_2/\text{MXene}$ structure and $\text{Ni}_3(\text{HITP})_2$ powder was analyzed using XPS. From the XPS spectra, we observed no significant difference in the Ni 2p spectra between $\text{Ni}_3(\text{HITP})_2/\text{MXene}$ and $\text{Ni}_3(\text{HITP})_2$ powder, indicating that the chemical environment of Ni in these two samples is the same.

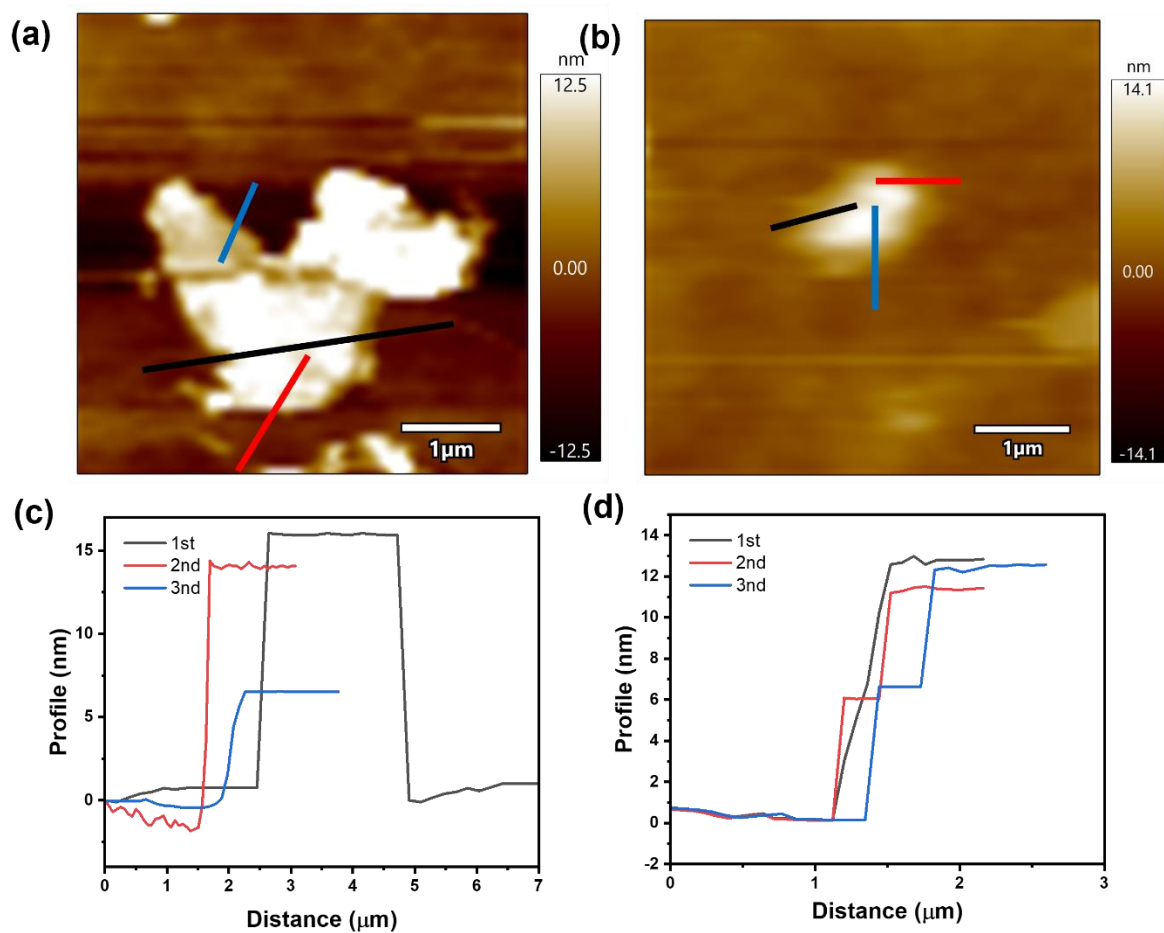


Figure S9. (a-b) Additional AFM images of monodispersed $\text{Ni}_3(\text{HITP})_2/\text{MXene}$ nanosheets on Si surfaces. (c-d) The second row presents the height profiles of (a-b), respectively.

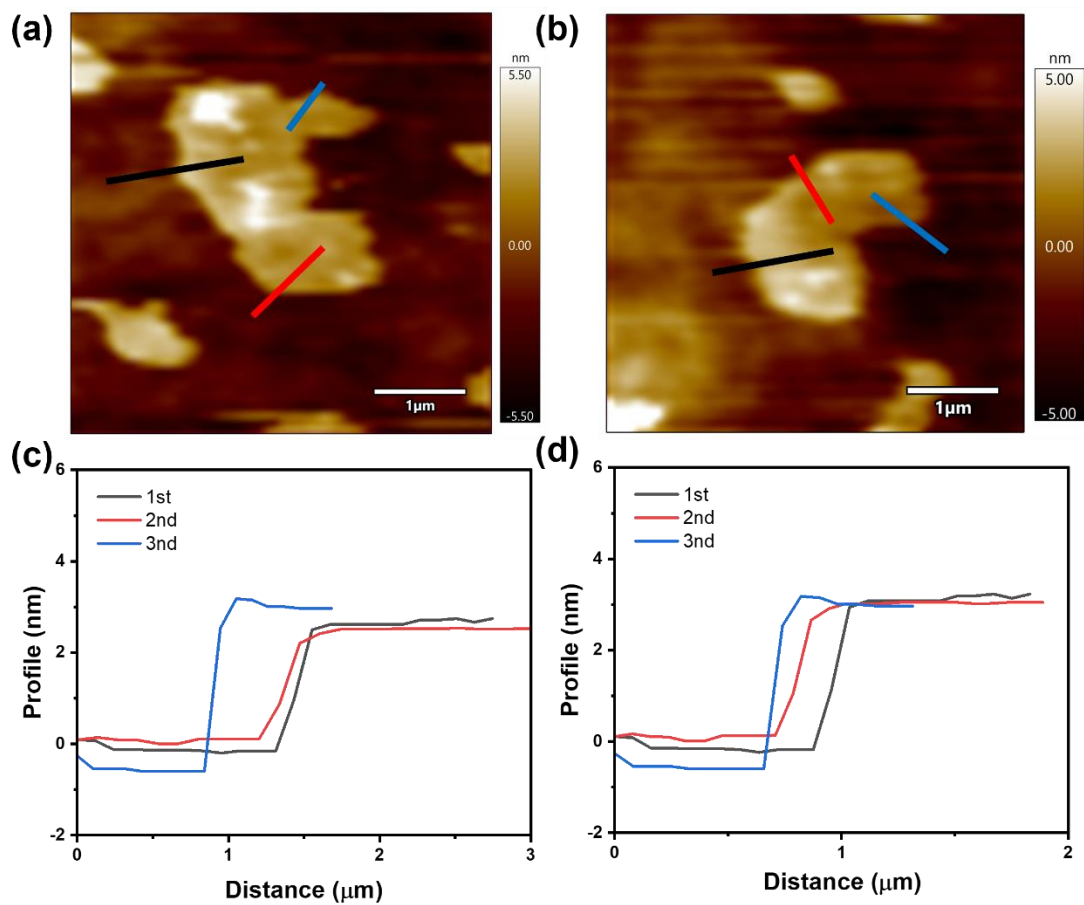


Figure S10. (a-b) Additional AFM images of monodispersed MXene nanosheets on Si surfaces.

(c-d) The second row presents the height profiles of (a-b), respectively.

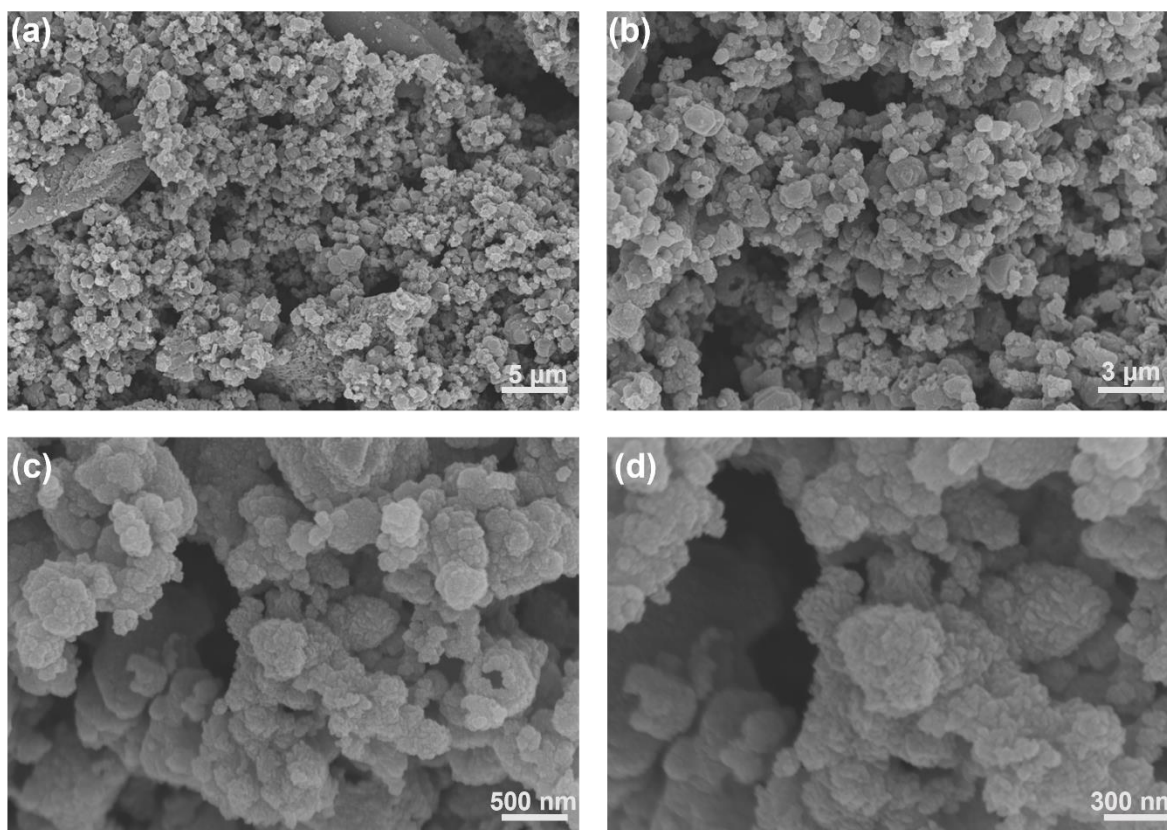


Figure S11. (a-d) SEM images of $\text{Ni}_3(\text{HITP})_2$ powder obtained by the conventional hydrothermal method.

Note: The morphology of $\text{Ni}_3(\text{HITP})_2$ powder was characterized using SEM. The $\text{Ni}_3(\text{HITP})_2$ powder was placed on a clean silicon substrate and then mounted onto the sample holder of the SEM. SEM images of the $\text{Ni}_3(\text{HITP})_2$ powder were collected at an accelerating voltage of 5 kV. The SEM images of the $\text{Ni}_3(\text{HITP})_2$ powder sample exhibited irregularly arranged particulate crystals.

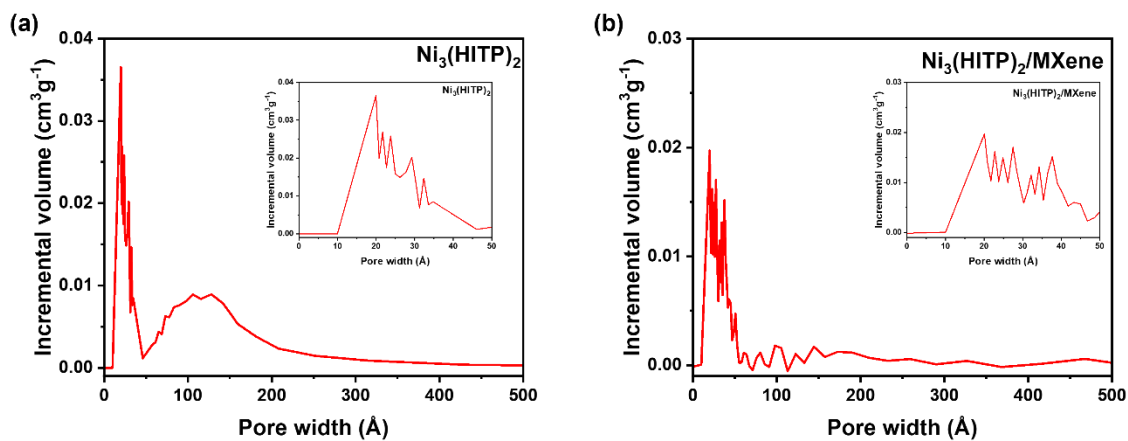


Figure S12. (a-b) Pore size distribution of the Ni₃(HITP)₂/MXene and Ni₃(HITP)₂ powder as shown in Figure 2i, respectively.

Note: The pore size distribution of both Ni₃(HITP)₂/MXene and Ni₃(HITP)₂ is mainly centered around 2 nm. However, there is a possible distribution of Ni₃(HITP)₂ pore size around 12 nm, which may be due to the gaps between the particles due to the stacking of Ni₃(HITP)₂.

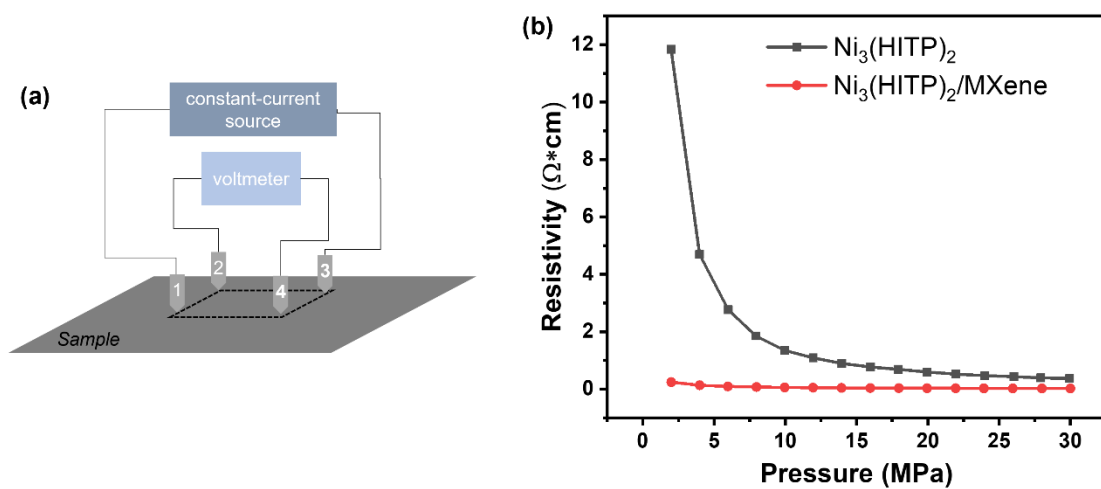


Figure S13. (a) Schematic diagram of the four-probe method for measuring resistance. (b) Resistivity curve of the $\text{Ni}_3(\text{HITP})_2/\text{MXene}$ heterostructure and $\text{Ni}_3(\text{HITP})_2$ powders measured by a standard four-point method as a function of pressure, respectively.

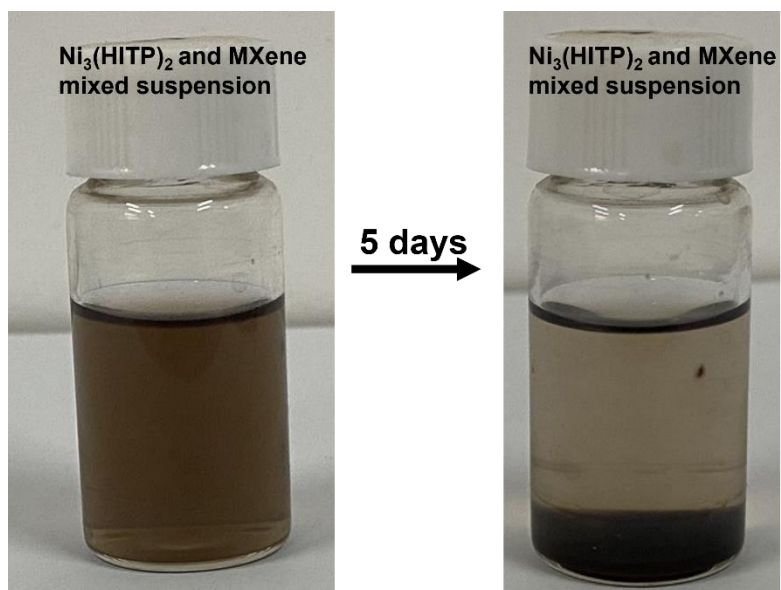


Figure S14. Optical photographs of Ni₃(HITP)₂/MXene and Ni₃(HITP)₂ mixed suspension both prior to and after being left at room temperature for a duration of five days.

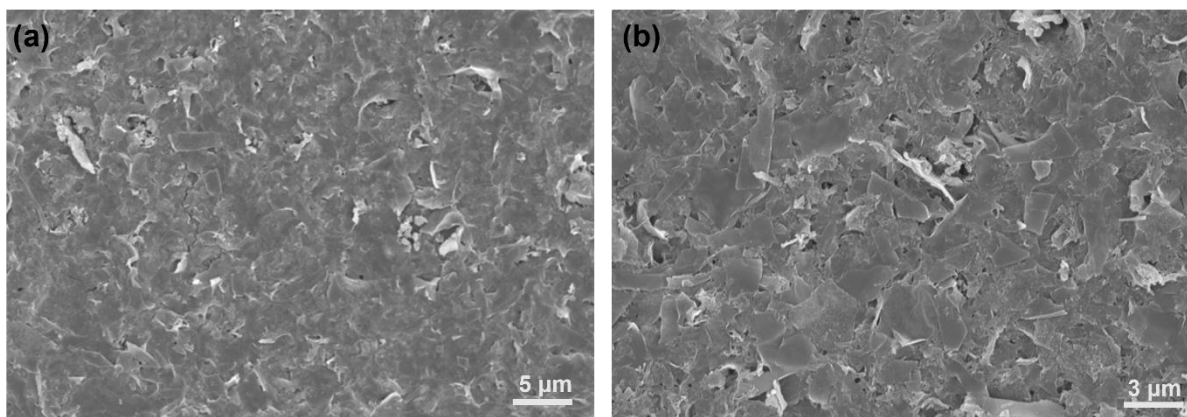


Figure S15. (a-b) Top-view SEM images of the $\text{Ni}_3(\text{HITP})_2/\text{MXene}$ films.

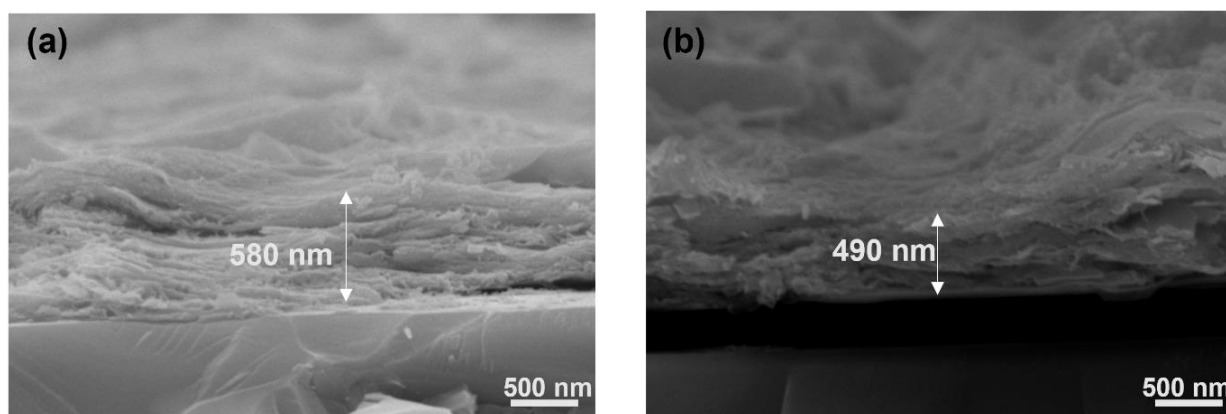


Figure S16. (a-b) Cross-sectional SEM images of a series of $\text{Ni}_3(\text{HITP})_2/\text{MXene}$ films on Si substrates with tunable thickness. Solid concentration and solution volume used for films: a) $C_{\text{Ni}_3(\text{HITP})_2/\text{MXene}} = 1 \text{ g}\cdot\text{L}^{-1}$, 20 μL ; b) $C_{\text{Ni}_3(\text{HITP})_2/\text{MXene}/\text{MXene}} = 0.8 \text{ g}\cdot\text{L}^{-1}$, 20 μL .

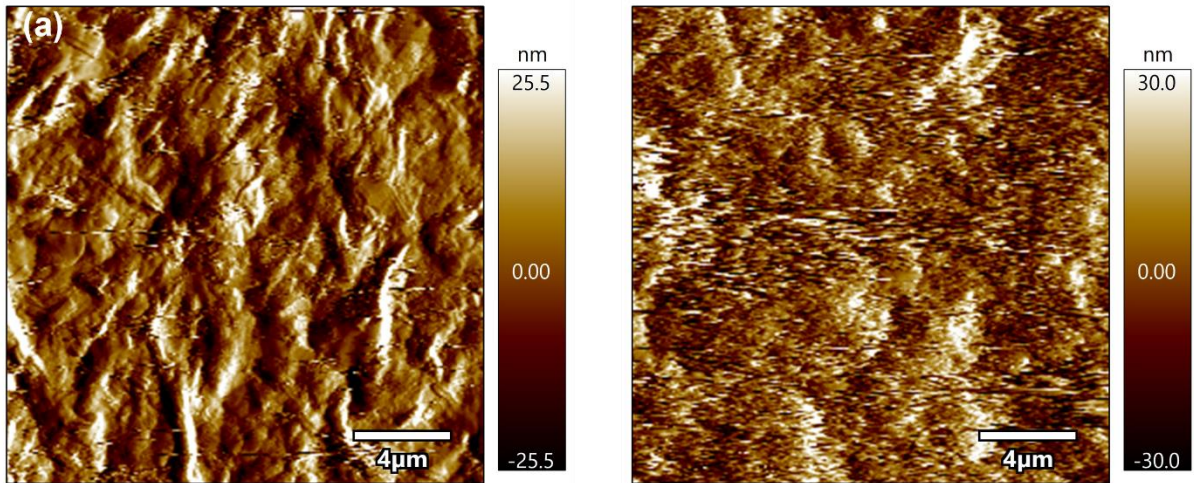


Figure S17. (a-b) AFM images of the (a) $\text{Ni}_3(\text{HITP})_2/\text{MXene}$ and (b) $\text{Ni}_3(\text{HITP})_2$ films.

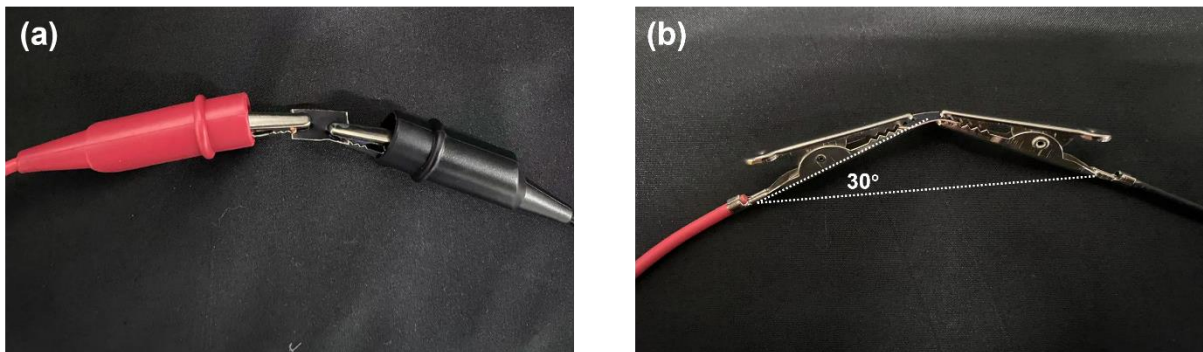


Figure S18. (a-b) Optical photograph of the $\text{Ni}_3(\text{HITP})_2/\text{MXene}$ films (a) before and (b) after bending at 30 degrees, corresponding to the schematic diagram in Figure 2h.

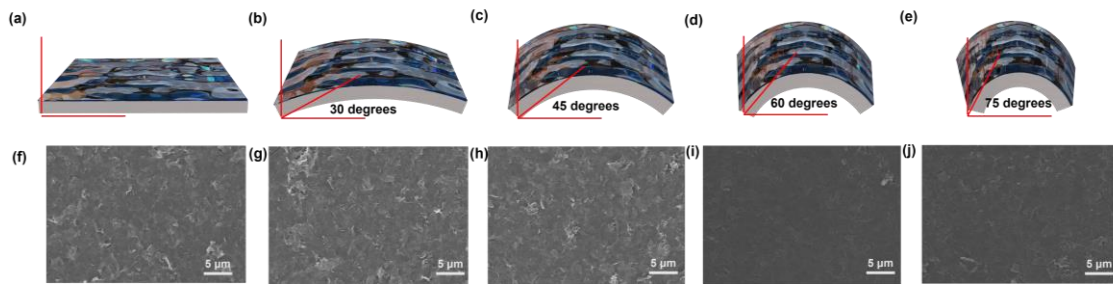


Figure S19 (a-e) Schematic bending diagram of $\text{Ni}_3(\text{HITP})_2/\text{MXene}$ films onto a flexible PVDF substrate before and after bending at different angles (0, 30, 45, 60, and 75 degrees) and their associated SEM images (f-j).

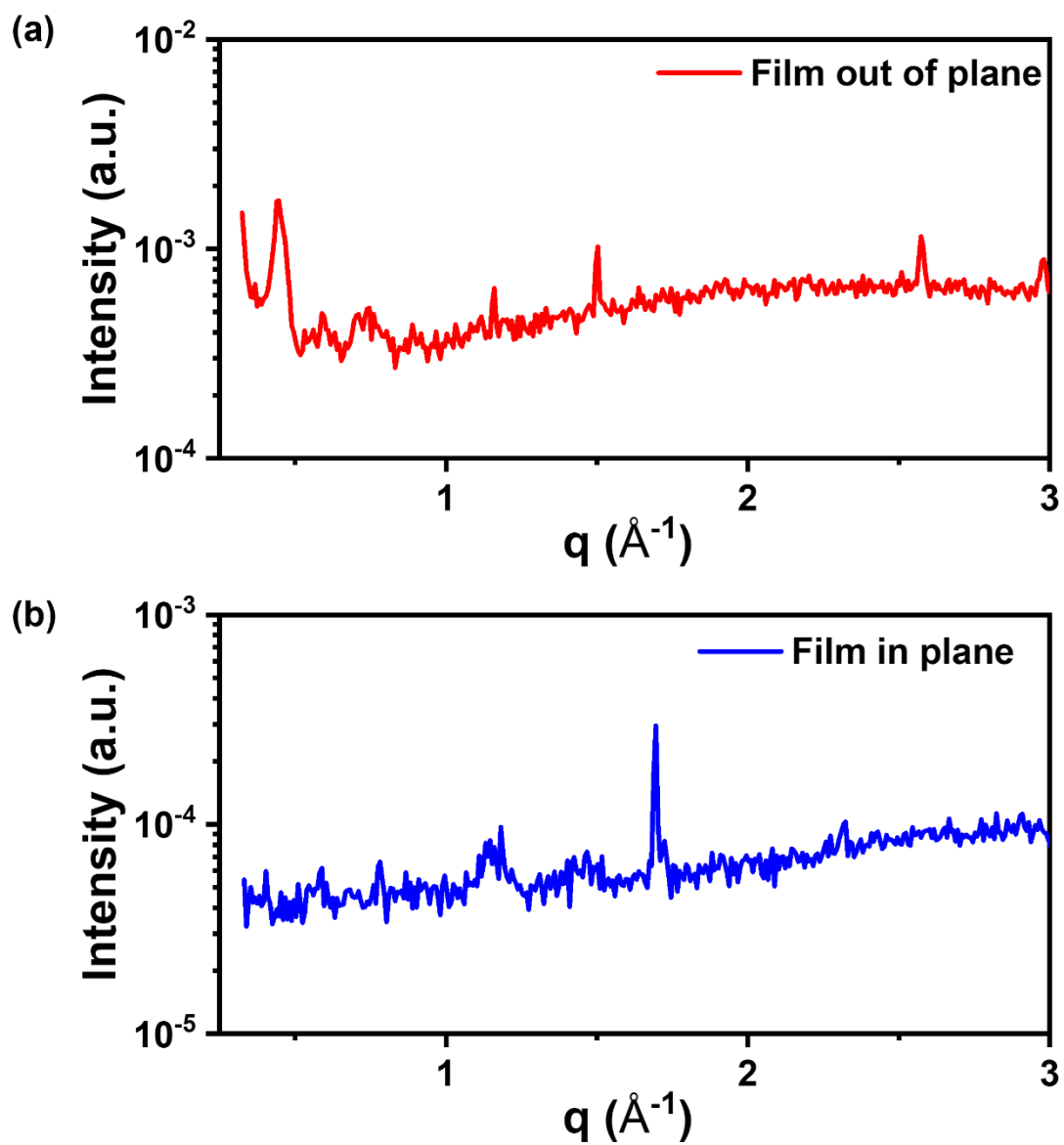


Figure S20. (a-b) Comparison of the out-of-plane and in-plane GIWAXS scattering profiles of the $\text{Ni}_3(\text{HITP})_2$ film.

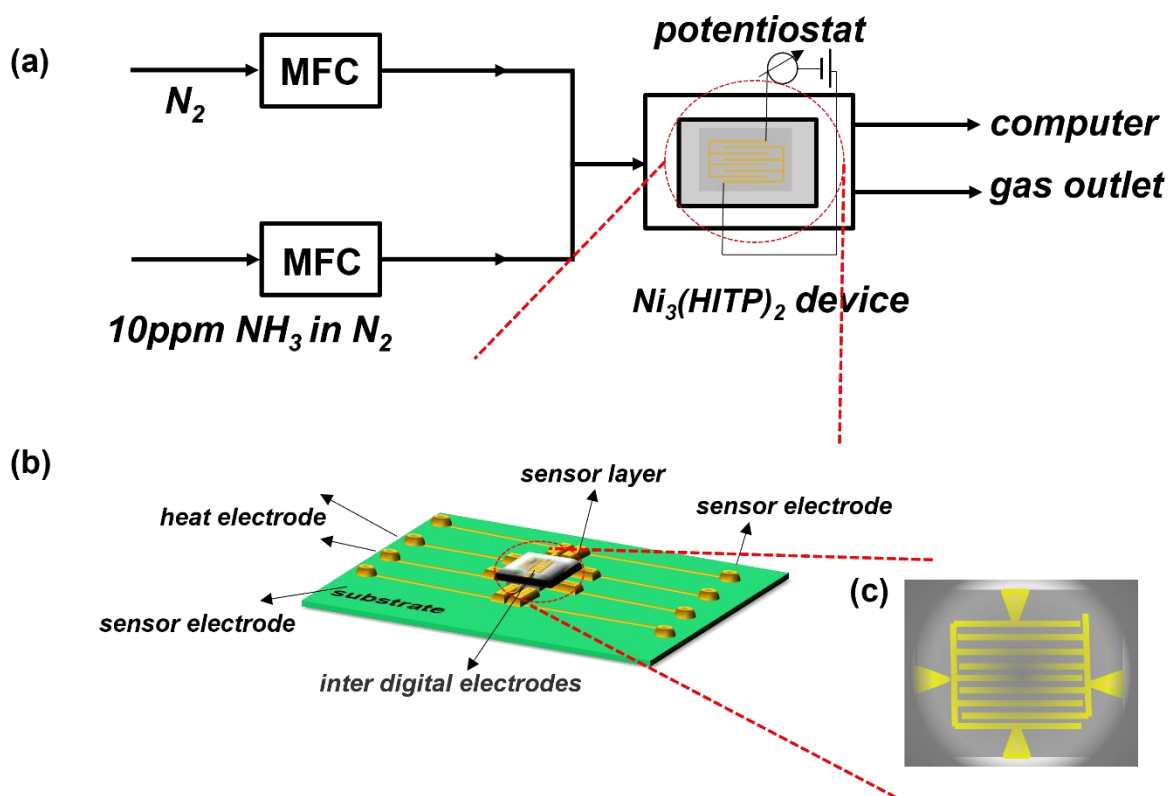


Figure S21. (a) Schematic diagram of the experimental apparatus. (b-c) Schematic diagram of the chip structure used within this study.

Note: The sensor performance of the sensors based on $Ni_3(HITP)_2/MXene$ and $Ni_3(HITP)_2$ was evaluated using a homemade gas sensing system^{S8}. The device was placed in the detection chamber, and the electrodes were connected to a digital multimeter. The entire experiment was conducted at room temperature. For typical experiments, the gas concentration and type were adjusted, and the resistance was monitored in real-time using a digital multimeter. The gas molecule concentration was accurately controlled by mass flow controllers (MFC). Before each test, the chamber was purged with nitrogen gas (N_2) for 15 minutes to stabilize the baseline resistance.

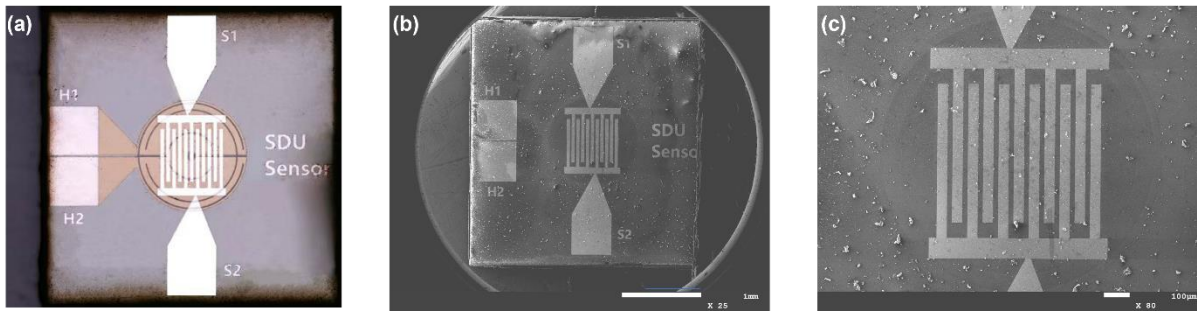


Figure S22. (a) Optical photographs of the sensor. (b-c) SEM images of the sensor.

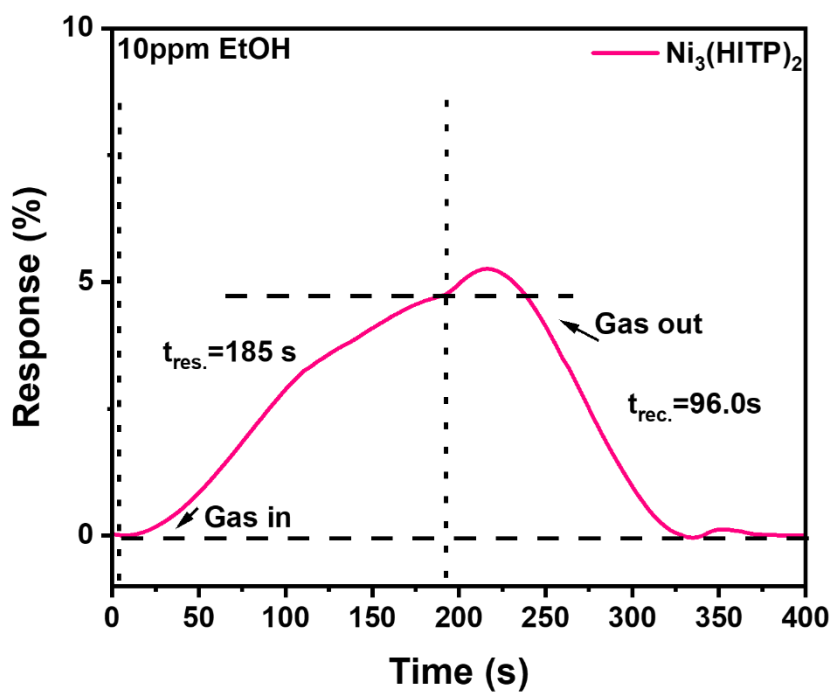


Figure S23. Dynamic response-recovery curve of the sensor based on $\text{Ni}_3(\text{HITP})_2$ to 10 ppm EtOH.

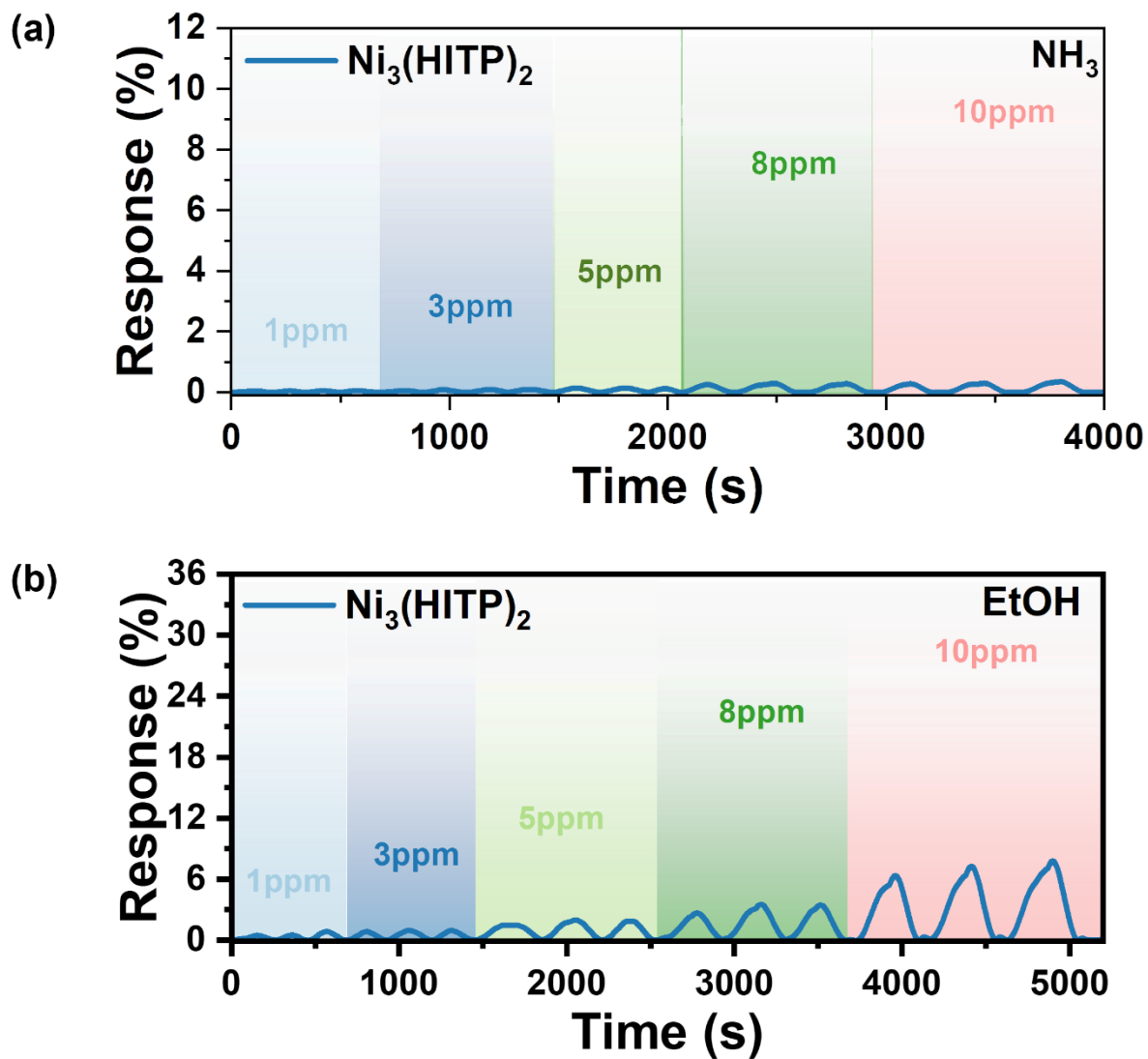


Figure S24. (a-b) Response-recovery curves of the $\text{Ni}_3(\text{HITP})_2$ coated sensor to different concentrations of NH_3 and EtOH.

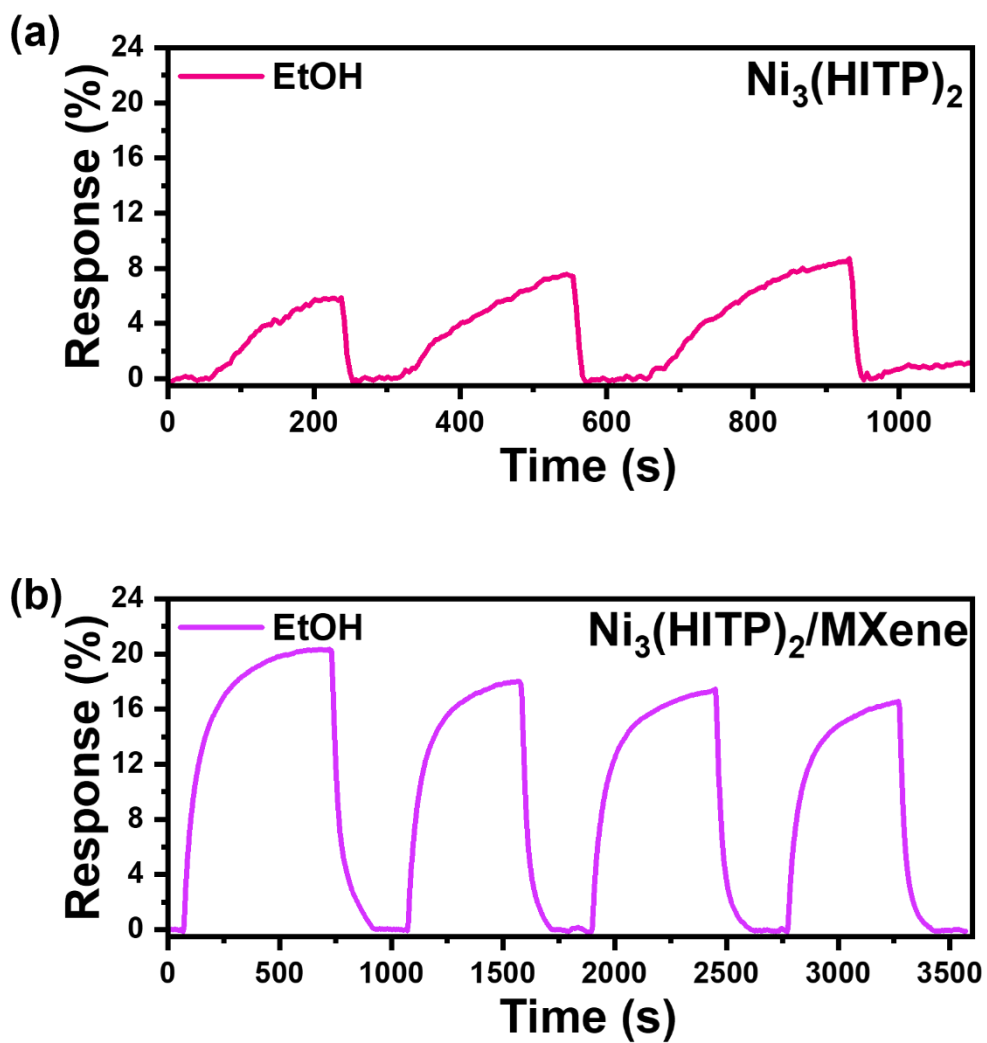


Figure S25. (a-b) Response-recovery curves of the sensors based on $\text{Ni}_3(\text{HITP})_2$ and $\text{Ni}_3(\text{HITP})_2/\text{MXene}$ to 10 ppm EtOH, respectively.

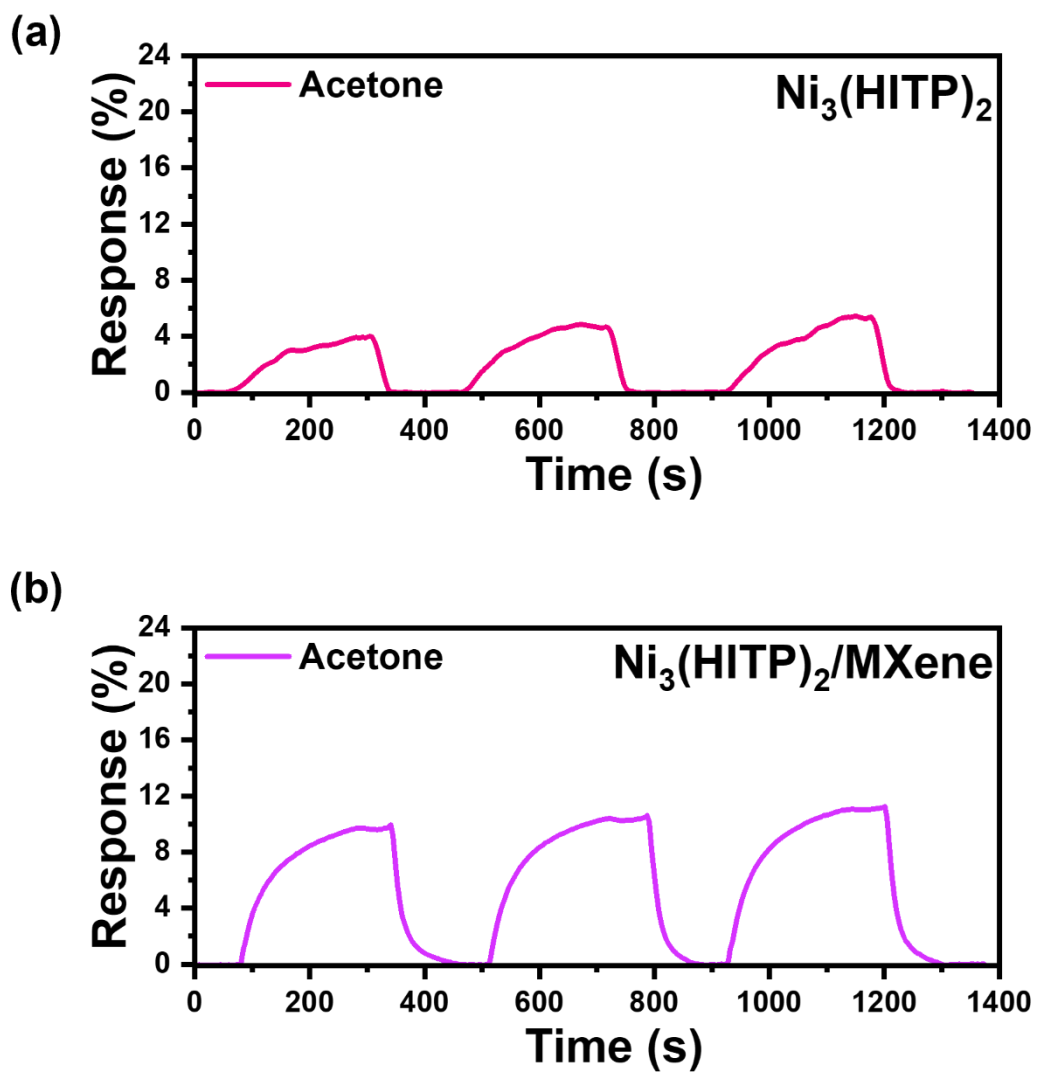


Figure S26. (a-b) Response-recovery curves of the sensors based on $\text{Ni}_3(\text{HITP})_2$ and $\text{Ni}_3(\text{HITP})_2/\text{MXene}$ to 10 ppm acetone, respectively.

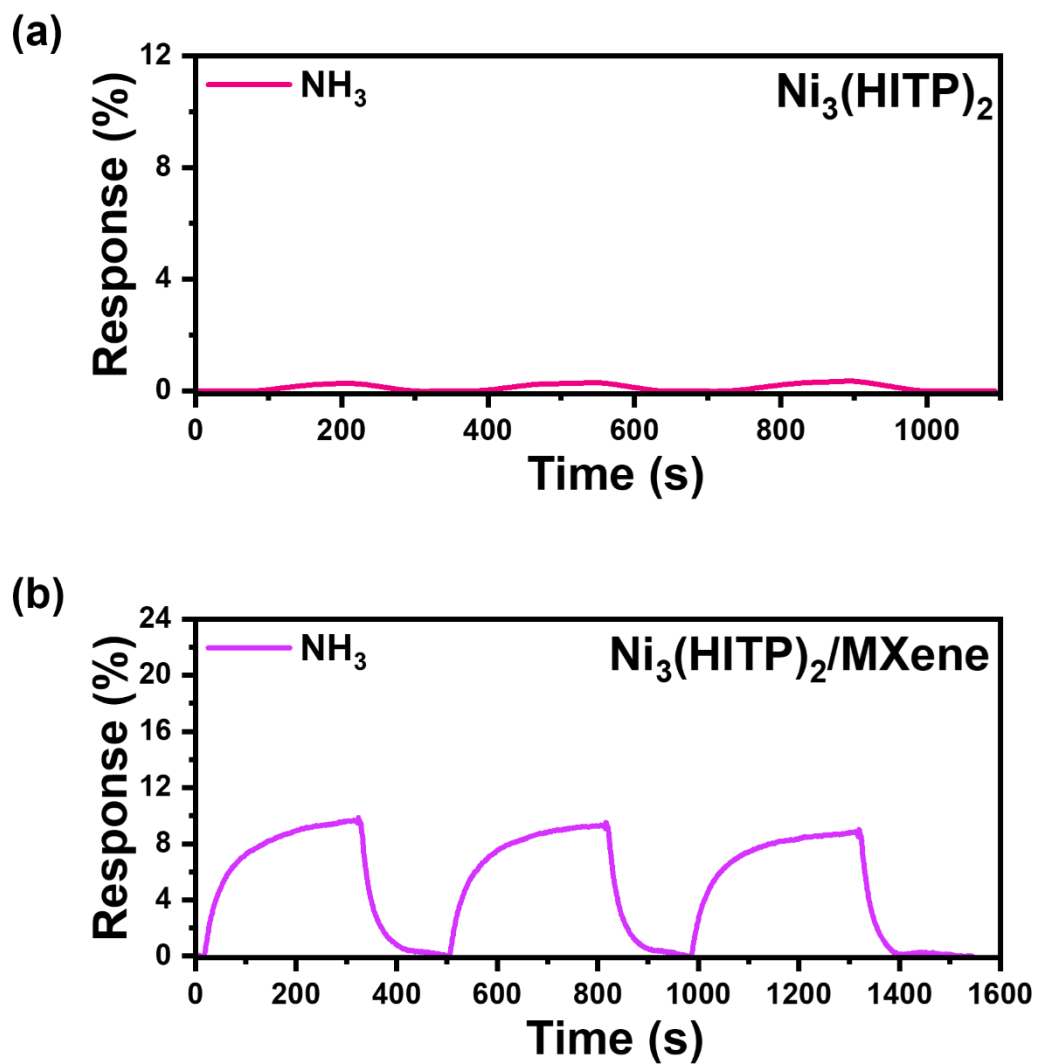


Figure S27. (a-b) Response-recovery curves of the sensors based on Ni₃(HITP)₂ and Ni₃(HITP)₂/MXene to 10 ppm NH₃, respectively.

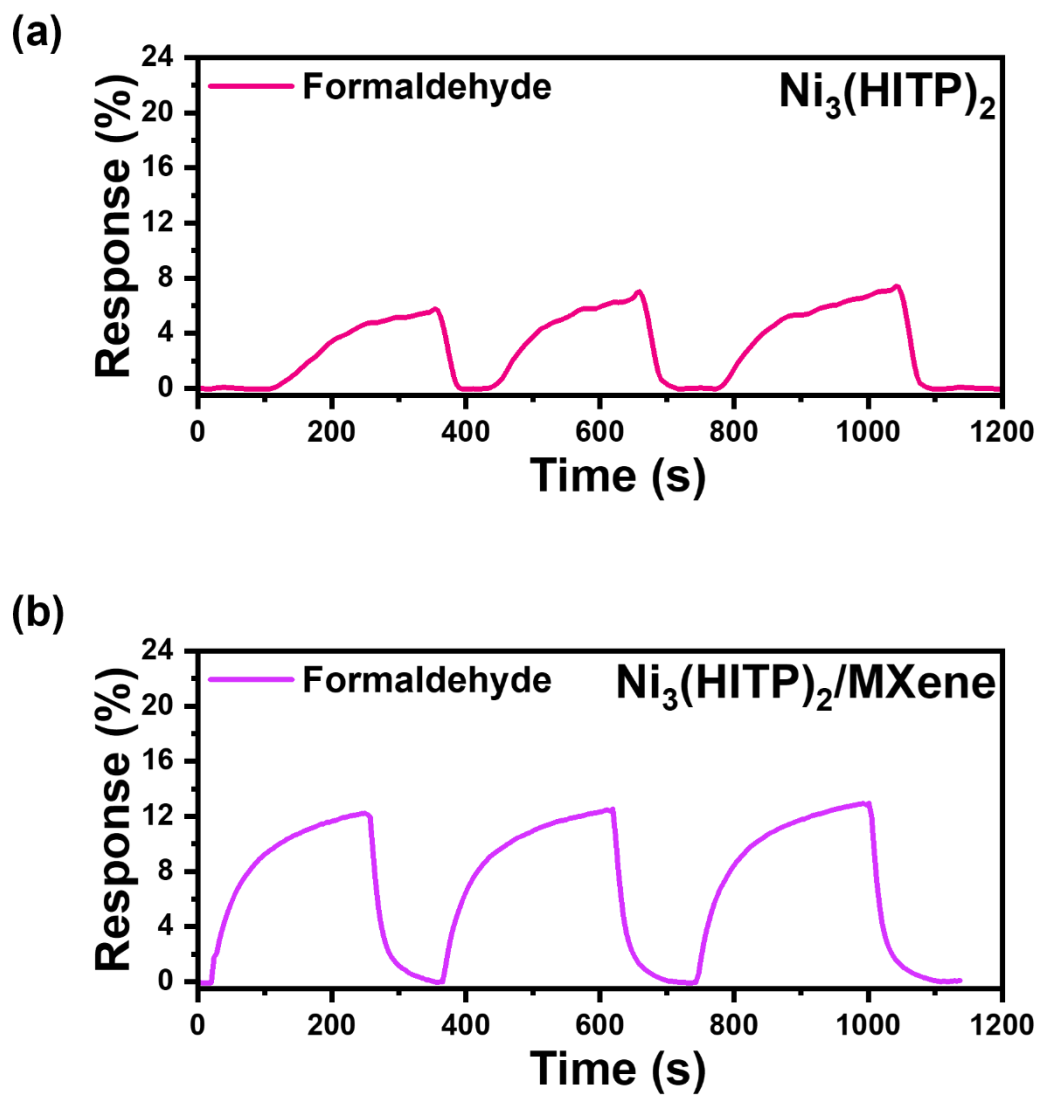


Figure S28. (a-b) Response-recovery curves of the sensors based on $\text{Ni}_3(\text{HITP})_2$ and $\text{Ni}_3(\text{HITP})_2/\text{MXene}$ to 10 ppm formaldehyde, respectively.

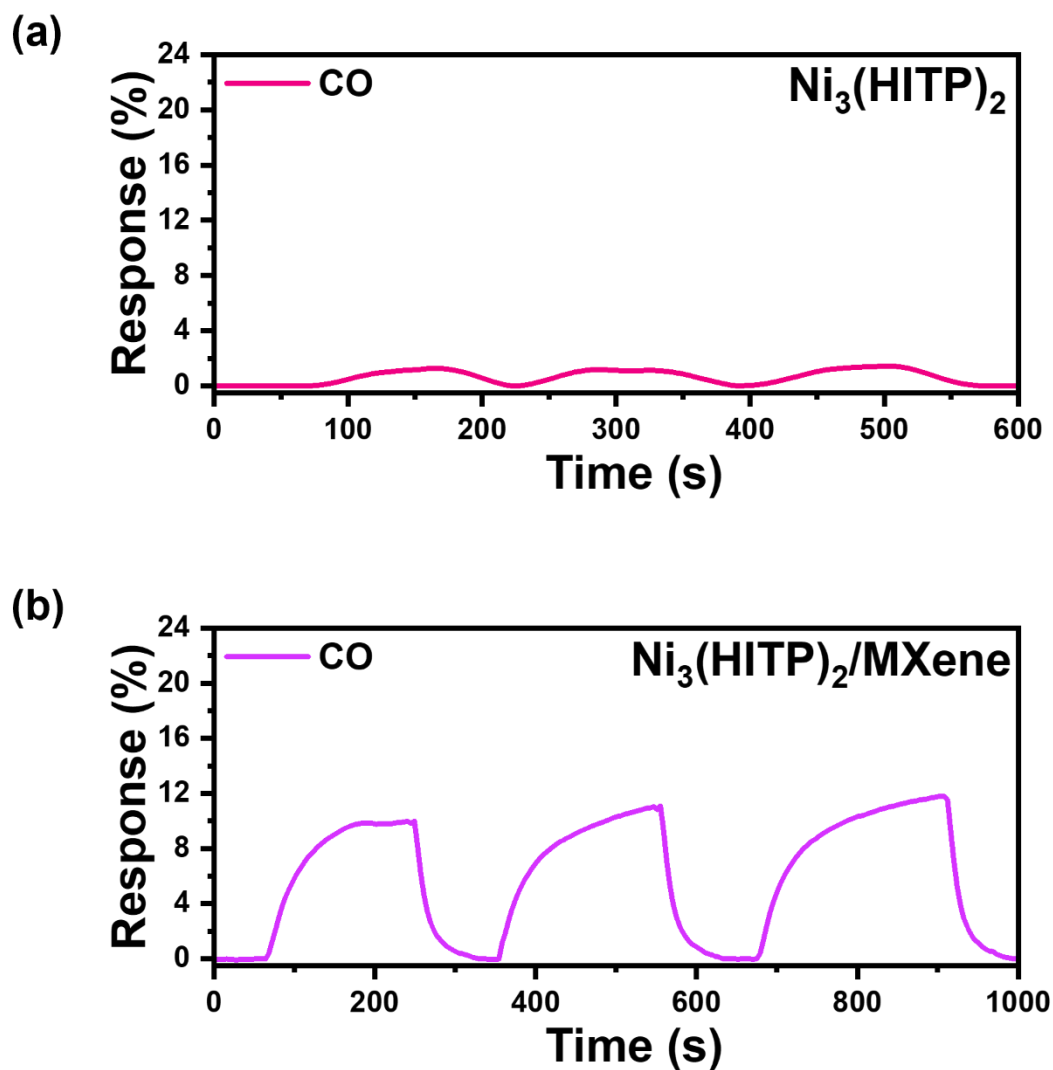


Figure S29. (a-b) Response-recovery curves of the sensors based on $\text{Ni}_3(\text{HITP})_2$ and $\text{Ni}_3(\text{HITP})_2/\text{MXene}$ to 10 ppm CO, respectively.

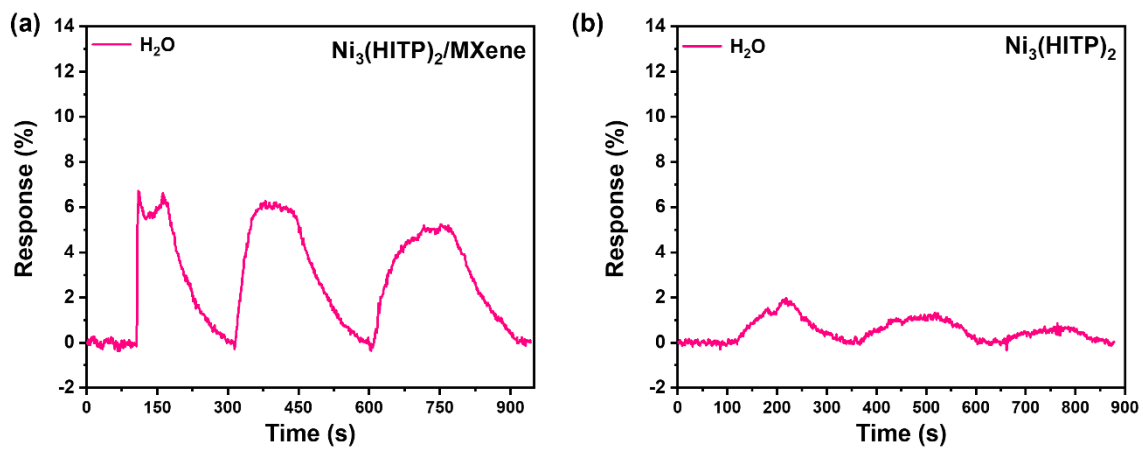


Figure S30. (a-b) Response-recovery curves of the sensors based on Ni₃(HITP)₂ and Ni₃(HITP)₂/MXene to 10 ppm water vapor, respectively.

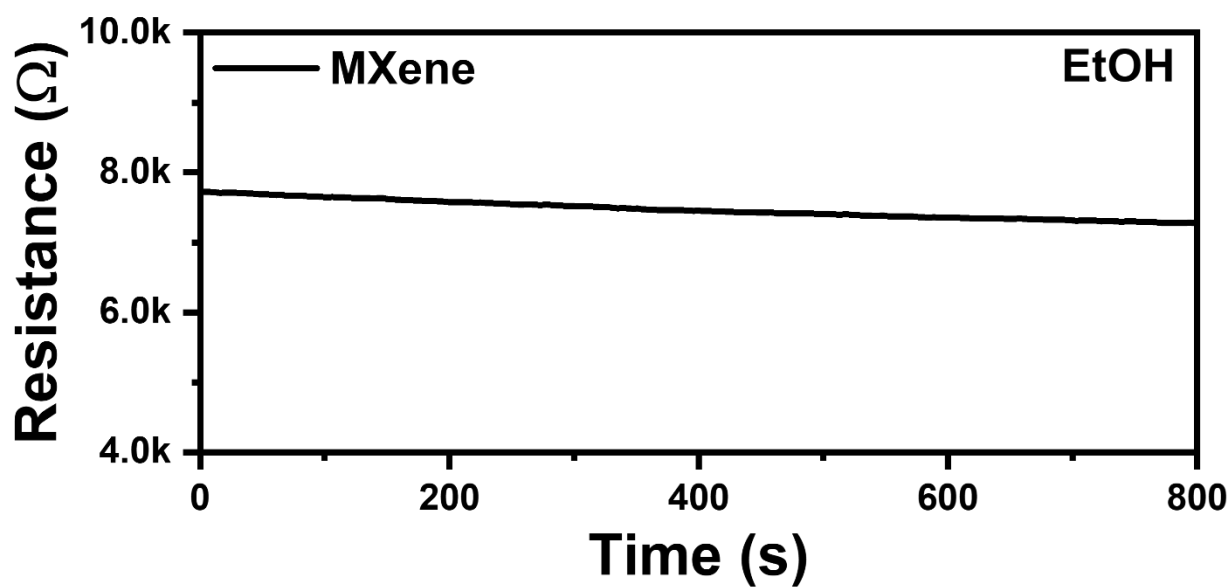


Figure S31. Resistance curve of the MXene coated sensor to 10 ppm EtOH.

Note: The MXene-based sensors did not exhibit a significant resistance response in the presence of 10 ppm EtOH.

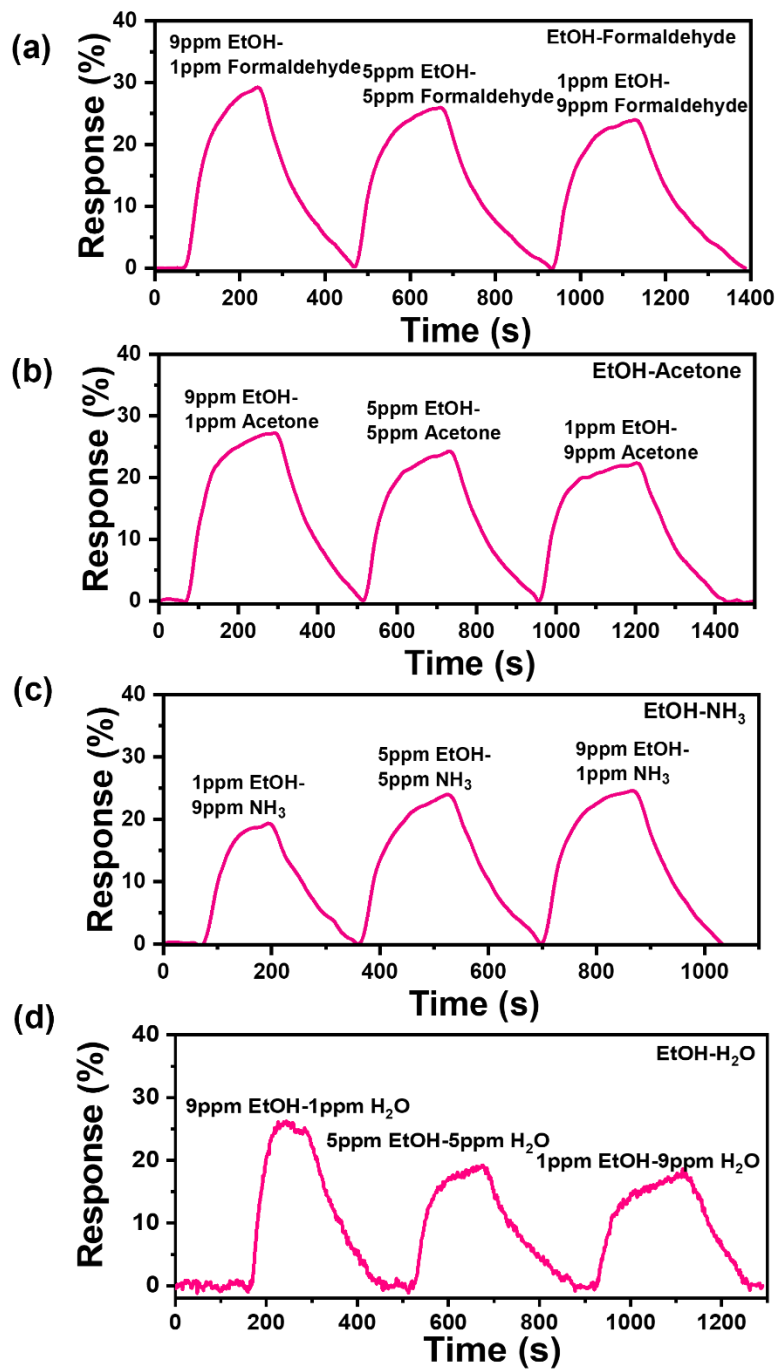


Figure S32. (a-d) Response-recovery curves of the $\text{Ni}_3(\text{HITP})_2/\text{MXene}$ coated sensors placed in mixed gas environments with different concentrations (1, 5, 9 ppm) and types (EtOH, acetone, formaldehyde, NH_3 , H_2O).

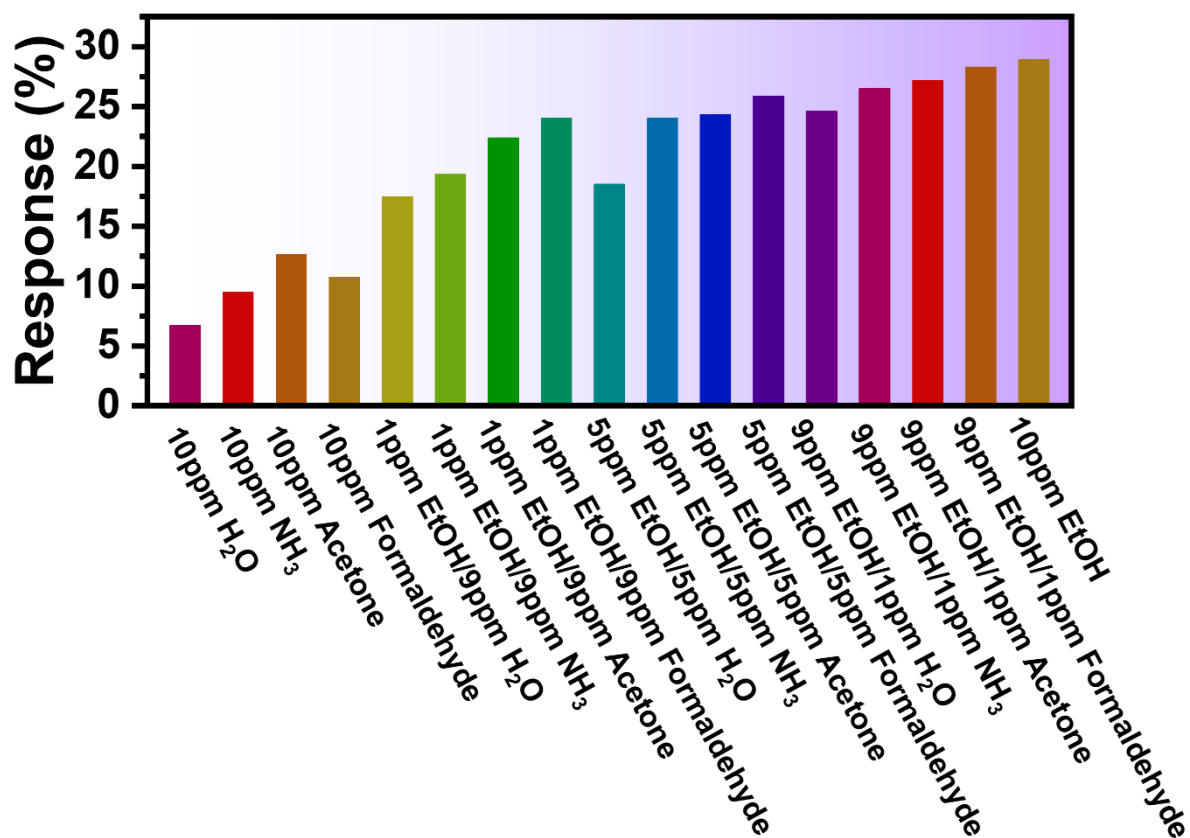


Figure S33. Bar graph of the response of the Ni₃(HITP)₂/MXene coated sensors placed in mixed gas environments with different concentrations (1, 5, 9 ppm) and types (EtOH, acetone, formaldehyde, NH₃, H₂O).

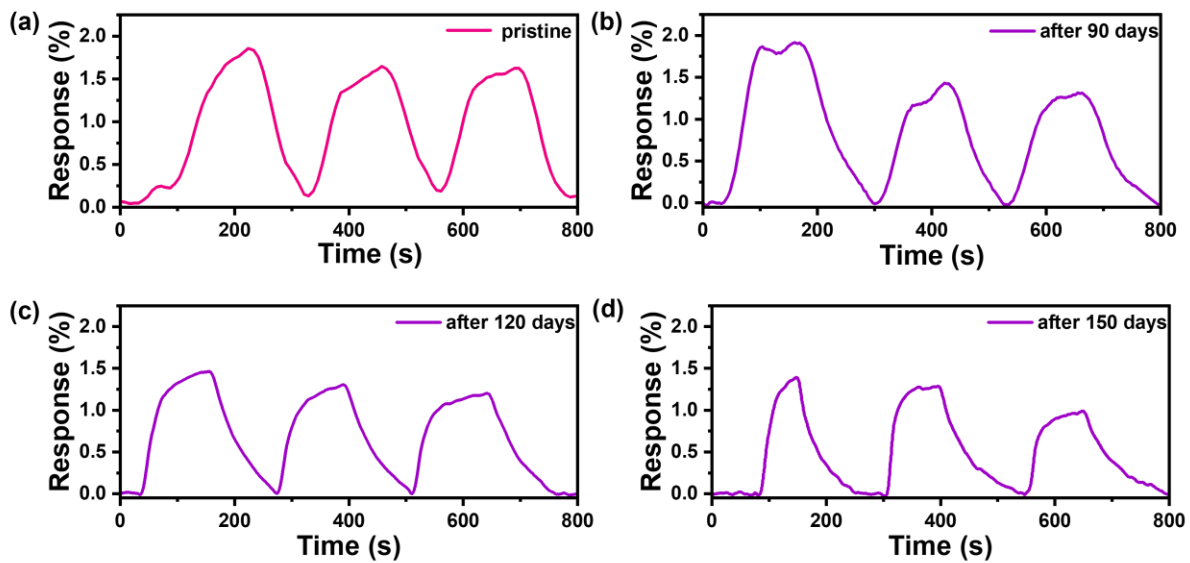


Figure S34. (a-d) Response-recovery curves of the $\text{Ni}_3(\text{HITP})_2/\text{MXene}$ coated sensors to 1 ppm EtOH after being stored for (a) 0, (b) 90, (c) 120, and (d) 150 days.

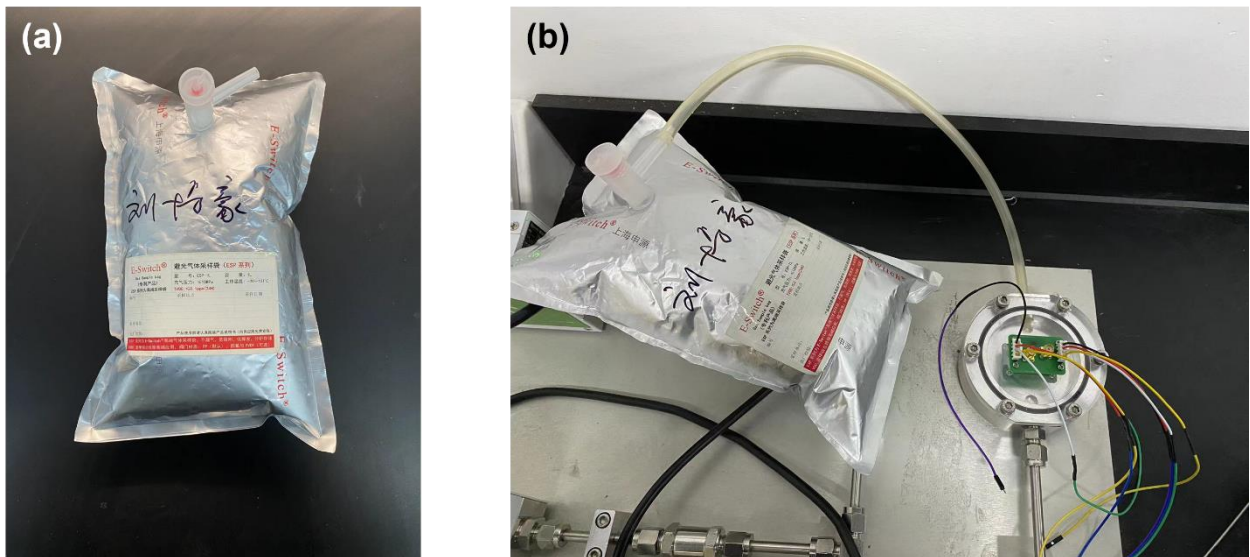
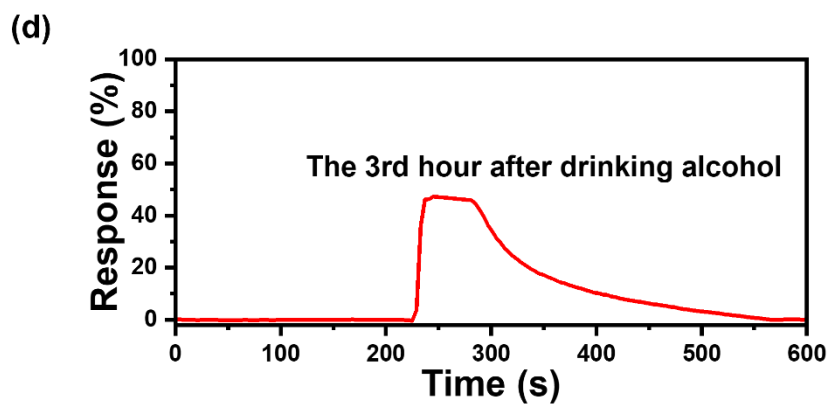
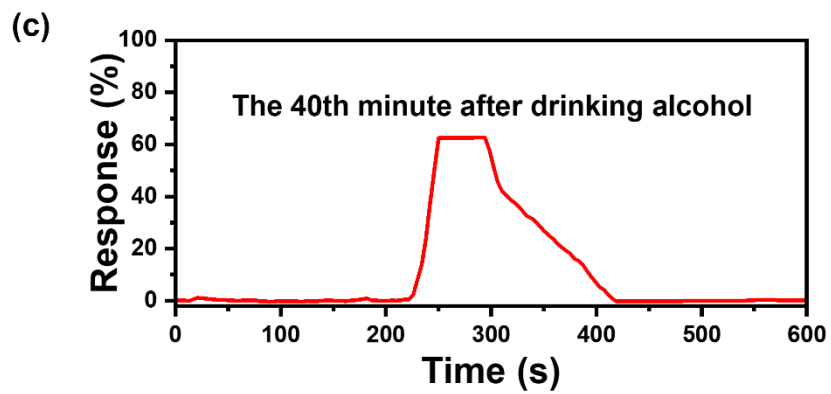
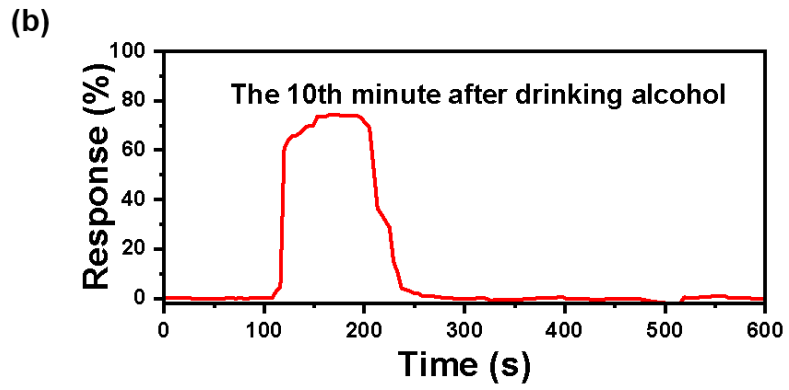
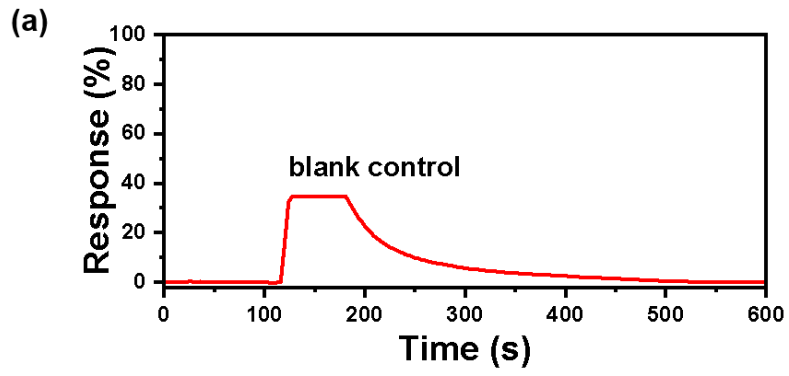


Figure S35. (a) Respiratory bags used to collect human respiratory gases. (b) The collection bag containing respiratory biomarker ethanol is connected to the customized room for sensing detection

Note: In the experiment, we employed a common method for collecting human breath gas, using a breath bag or breath sample collector, as illustrated in Figure S34. Participants were first instructed to consume alcohol for a specific duration, and then exhale into the breath bag or breath sample collector at specific time intervals. During the measurement process, the chip was placed within a custom chamber with stretchable metal contacts. The collection bag containing the breath biomarker ethanol was connected to the custom chamber. The relative changes in the target breath biomarker ethanol were evaluated by measuring the resistance change before and after gas adsorption. Additionally, before data acquisition, the chamber was purged with nitrogen gas (N_2) for 15 minutes to stabilize the baseline resistance. N_2 was also used as a diluent to achieve the target concentration and for sensor regeneration.



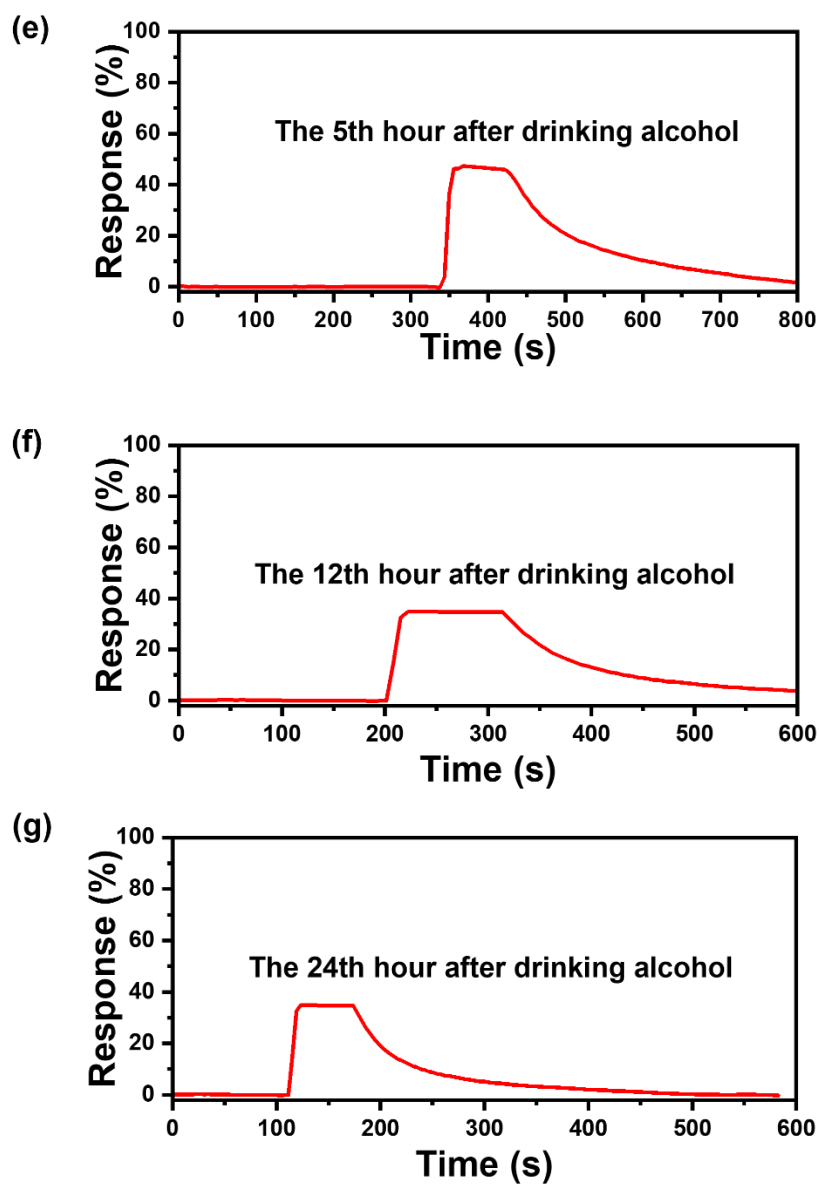


Figure S36. (a-g) Response-recovery curves of human breath after alcohol consumption at (a) 0 h, (b) 10 minutes, (c) 40 minutes, (d) 3 h, (e) 5 h, (f) 12 h, (g) 24 h.

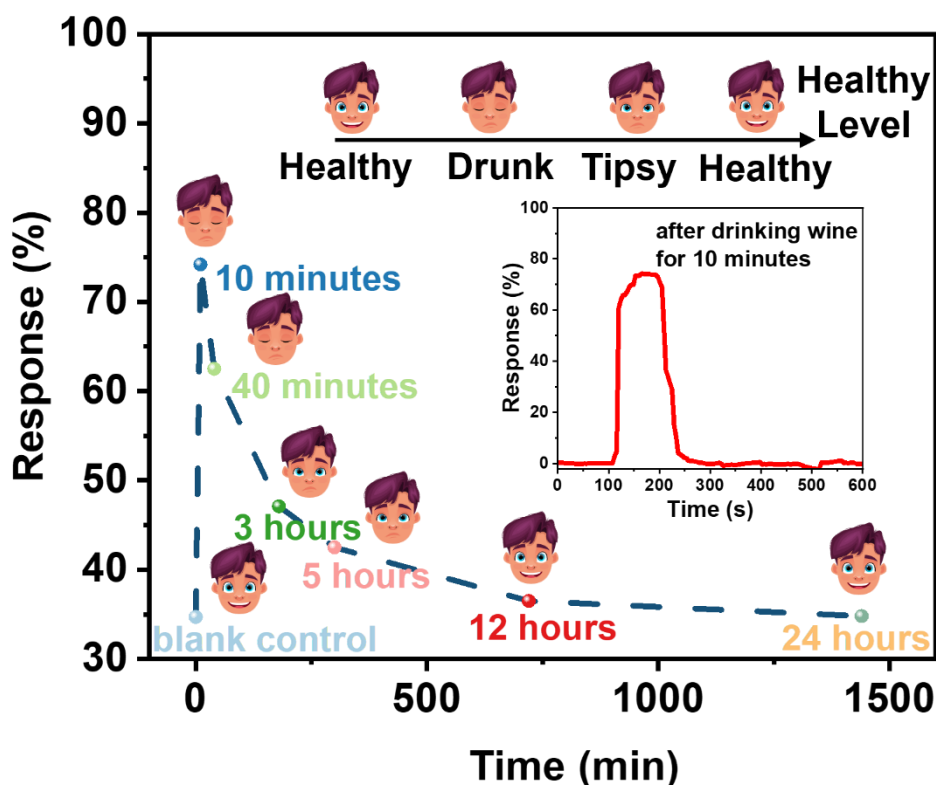


Figure S37. Real-time monitoring of human breath gas after alcohol consumption within 24 hours.

Note: In the experiment, we recorded real-time changes in human respiratory resistance within 24 hours after drinking alcohol. The results showed that compared to the baseline, there was a significant change in respiratory response within only 40 minutes after drinking alcohol, marking the beginning of the drunken state. Within the following 3-5 hours, the respiratory response gradually stabilizes, reflecting the individual's transition from a drunken state to a mildly intoxicated state. In the end, between 12-24 hours, the respiratory response was very similar to the baseline, indicating that the patient had returned to a normal state.

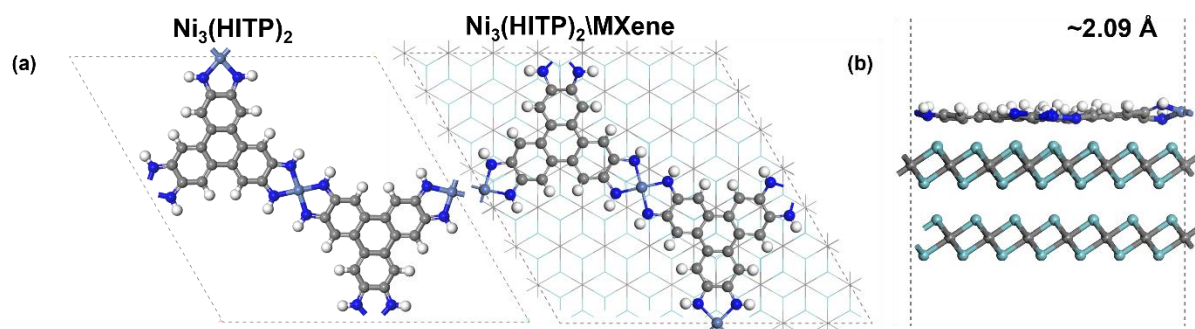


Figure S38. (a) Top view of the calculated $\text{Ni}_3(\text{HITP})_2$ and $\text{Ni}_3(\text{HITP})_2/\text{MXene}$ heterostructure, respectively; (b) Side view of $\text{Ni}_3(\text{HITP})_2/\text{MXene}$ heterostructure after relaxing, respectively.

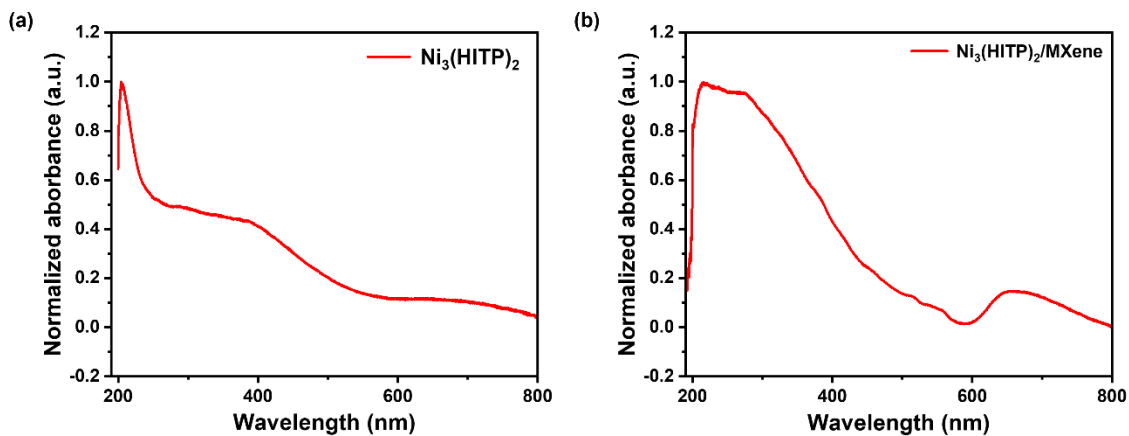


Figure S39. (a-b) UV-Vis absorption spectra of (a) $\text{Ni}_3(\text{HITP})_2$ and (b) $\text{Ni}_3(\text{HITP})_2/\text{MXene}$.

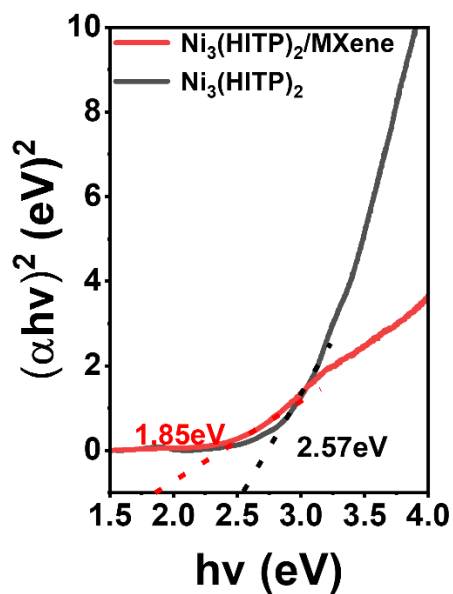


Figure S40. Calculated optical bandgaps of the $\text{Ni}_3(\text{HITP})_2/\text{MXene}$ and $\text{Ni}_3(\text{HITP})_2$ based on UV-Vis spectra.

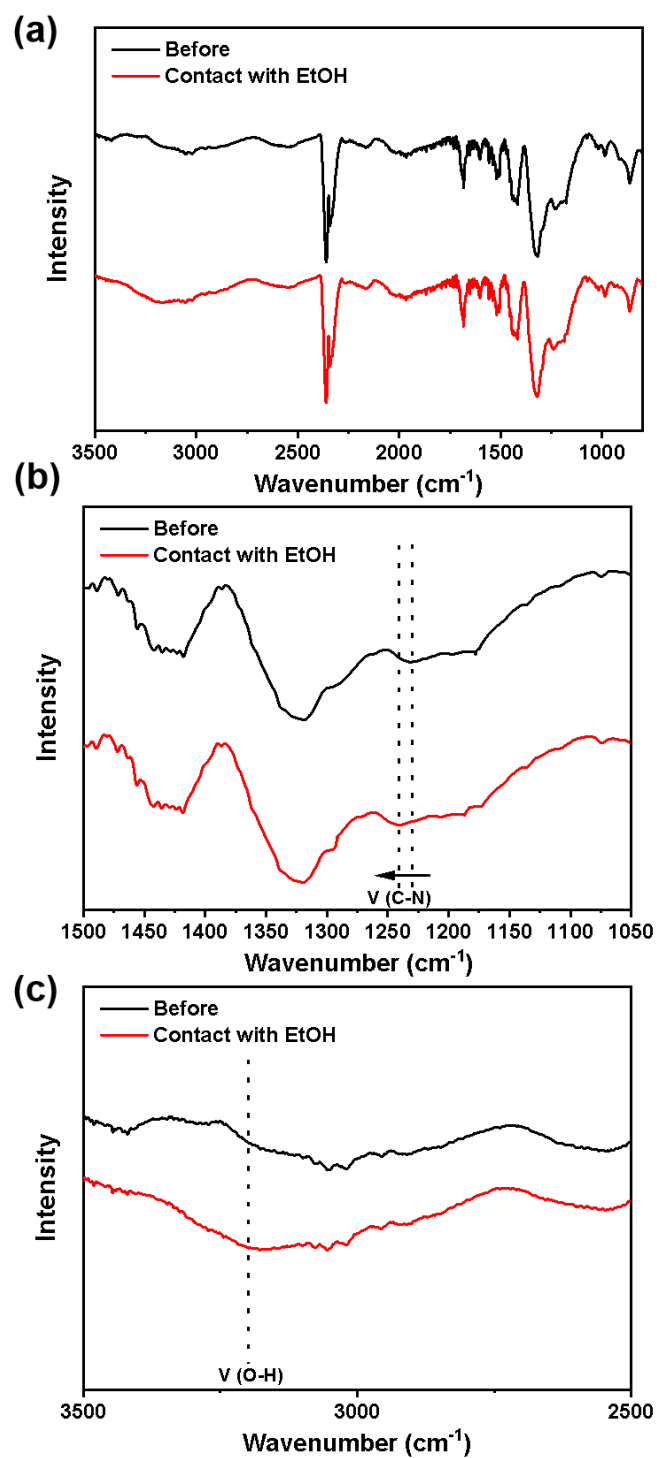


Figure S41. (a-c) FTIR spectra of the $\text{Ni}_3(\text{HITP})_2/\text{MXene}$ powder before and after adsorption of EtOH at relatively low concentration (10 ppm).

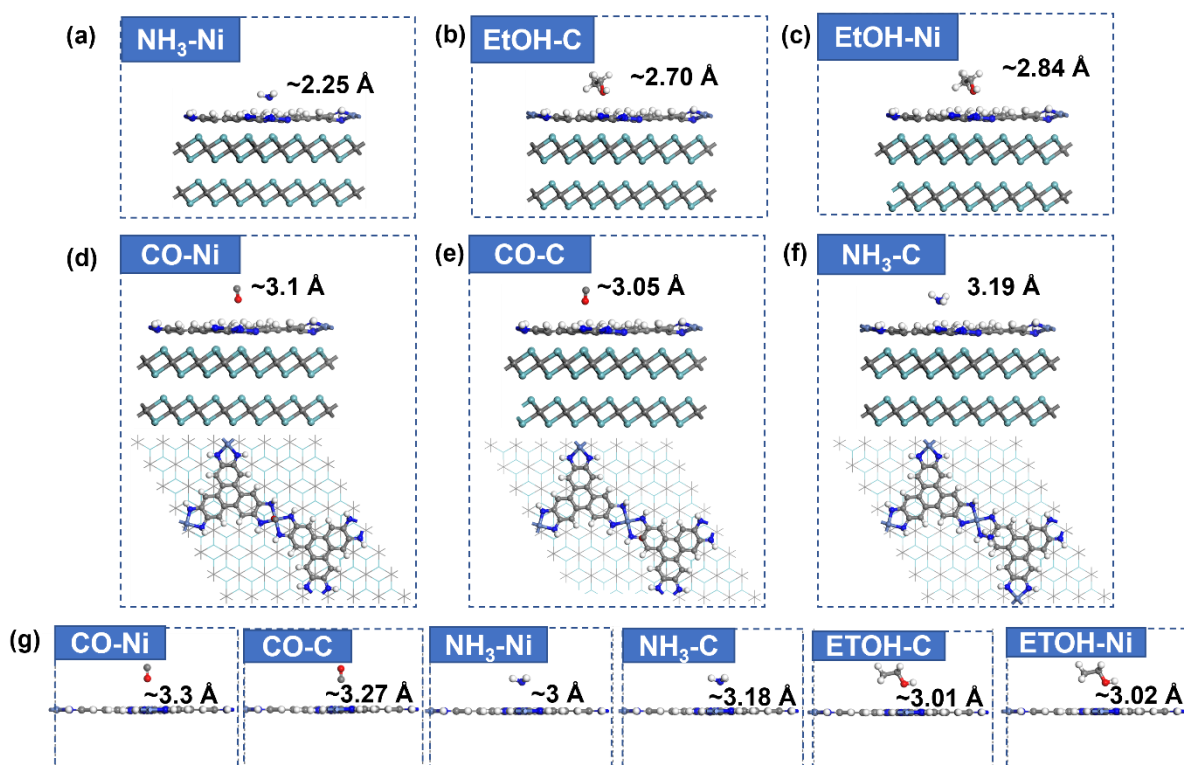


Figure S42. Physisorption of CO, NH₃ and EtOH on Ni₃(HITP)₂/MXene heterostructure and the monolayer Ni₃(HITP)₂. (a-f) Side and top views of the sensing molecules on Ni₃(HITP)₂/MXene heterostructure. (e) Side view of CO, NH₃ and EtOH on Ni₃(HITP)₂.

Table S1. Conductivity comparison of the Ni₃(HITP)₂/MXene with other materials in the literature. Note that the Ni₃(HITP)₂ film we prepared just by drop-casting shows a conductivity of 1.2 S m⁻¹, which is lower than that of the Ni₃(HITP)₂ pellet prepared by compression, highlighting the advantage of the solution processability of the resultant Ni₃(HITP)₂/MXene system.

Materials	State	Conductivity (S m ⁻¹)	Ref.
Ni ₃ (HITP) ₂	Powder	2.7 × 10 ²	This work
Ni ₃ (HITP) ₂	Film	1.2	This work
Ni ₃ (HITP) ₂ /MXene	Powder	4.8 × 10 ³	This work
Ni ₃ (HITP) ₂ /MXene	Film	5.3 × 10 ⁵	This work
Cu ₃ (HHTP) ₂	Powder	0.2	32
Cu ₃ (HITP) ₂	Powder	20	33
Ni ₃ (HHTP) ₂	Powder	10	34
NiPc-Ni	Powder	~7.2 × 10 ⁻²	35
NiPc-Cu	Powder	1.4	35
Cu-HHTP-THQ	Powder	~ 2.5 × 10 ⁻³	35
ZIF-8/rGO	Powder	64	37
ZIF-8/SWCNT	Powder	5.6	38
UiO-66/CNT	Powder	~ 1.25 × 10 ³	39
MOF/PEDOT	Powder	0.7	40
MOF/ppy	Powder	~ 1.15 × 10 ²	41
La ₄ (HTTFTB) ₄ (1)	Powder	5.4 × 10 ⁻⁴	S13
La(HTTFTB) (2)	Powder	2.7 × 10 ⁻⁴	S13
La ₄ (TTFTB) ₃ (3)	Powder	3.1 × 10 ⁻⁷	S13
LaHHTP	Powder	0.9 × 10 ⁻²	S14
HoHHTP	Powder	5.0	S14

DDA-Cu	Powder	9.4	S15
<i>c</i> -HBC-12O-Cu	Powder	3.31	S16
Cu ₄ DHTTB	Powder	20	S17
Cu ₂ (OHPTP)	Powder	10	S18
Ni ₃ (HATI_C1) ₂	Powder	1.1	S19
Ni ₃ (HATI_C3) ₂	Powder	0.45	S19
Ni ₃ (HATI_C4) ₂	Powder	0.09	S19
Ni-CAT-1-on-SLG	Film	4×10^4	27
Co ₉ (HOTP) ₄	Film	0.33	S20
Cu ₃ (HOTP) ₂	Film	29	S20
Fe ₃ (THT) ₂ (NH ₄) ₃	Film	3.4	S20
Ag ₃ (BHT) ₂	Film	3.6×10^4	S20
Ni ₃ (BHT) ₂	Film	1.6×10^4	S20
Ni ₂ [Ni(IPc)]	Film	0.2	S20
Ni/Fe(NDC)	Film	1.0×10^{-3}	S20
Cu ₃ (BTC) ₂ (HKUST-1)	Film	7.0	S20

Table S2. Sensing performance comparison the gas sensors based on Ni₃(HITP)₂/MXene with other ones based on pure MOF or MOF-based composite materials, and most MOS-based sensors to EtOH and NH₃.

Materials	T (°C)	Gas	Conc. (ppm)	Response (%)	LOD (ppm)	Ref.
Ni ₃ (HITP) ₂	RT	NH ₃	10	0.25	N.A.	This work
Ni ₃ (HITP) ₂	RT	EtOH	10	6.05	0.48	This work
Ni ₃ (HITP) ₂ /MXene	RT	NH ₃	10	9.46	0.25	This work
Ni ₃ (HITP) ₂ /MXene	RT	EtOH	10	28.8	0.005	This work
CuTCNQ	RT	NH ₃	50	0.1	10	31
CuTCNQF ₄	RT	NH ₃	99	4.34	10	31
Cu ₃ (HHTP) ₂	RT	NH ₃	80	0.7	2	32
Cu ₃ (HITP) ₂	RT	NH ₃	10	3	0.5	33
Ni ₃ (HHTP) ₂	RT	NH ₃	80	0	0	32
NiPc-Ni	RT	NH ₃	80	~45	0.05–0.31	35
NiPc-Cu	RT	NH ₃	80	~45	0.16–0.33	35
Cu-HHTP-THQ	RT	NH ₃	100	20	0.02	36
Cu-BTC@GO-25	RT	NH ₃	100	4	100	52
Ni-CAT-1-on-SLG	RT	NH ₃	100	6.75	0.01	27
SnS ₂ -SnO ₂	RT	NH ₃	10	1.2	10	56
Ti ₃ C ₂ T _x	RT	NH ₃	100	0.8	1.3×10 ⁻⁴	57
ZnO@ZIF-8@POM	RT	EtOH	100	30	N.A.	55
Cu ₃ (HHTP) ₂ (thick film)	RT	EtOH	200	2.3	N.A.	54
Cu ₃ (HHTP) ₂ (thin film)	RT	EtOH	100	40	N.A.	40
Cu ₃ (HITP) ₂	RT	EtOH	200	0.8	N.A.	44
CuO	260	EtOH	10	1.6	N.A.	S9
Gr-Fe ₂ O ₃	280	EtOH	1	4.8	N.A.	S9
MoO ₃	300	EtOH	100	32.4	N.A.	S9
MoS ₂	RT	EtOH	1	2	1	S10
SnO ₂	300	EtOH	100	55	N.A.	S9
Ti ₃ C ₂ T _x	RT	EtOH	100	1.7	N.A.	S11
Co-TCPP(Fe)/Ti ₃ C ₂ T _x -20	RT	EtOH	20	1.01	N.A.	S12

Table S3. Adsorption energies and distances of $\text{Ni}_3(\text{HITP})_2/\text{MXene}$ and $\text{Ni}_3(\text{HITP})_2$ for EtOH, NH_3 , and CO. E_{ad} is the adsorption energy and Δd is the distance between gas molecules and substrate. The unit of E_{ad} and Δd is eV and Å, respectively.

	CO-Ni	CO-C	NH_3 -Ni	NH_3 -C	EtOH-Ni	EtOH-C
$E_{\text{ad}}(\text{Ni}_3(\text{HITP})_2)$	-0.06	-0.10	-0.03	-0.08	-0.12	-0.15
Δd	3.30	3.27	3.00	3.18	3.02	3.01
$E_{\text{ad}}(\text{Ni}_3(\text{HITP})_2/\text{MXene})$	-0.09	-0.13	-0.37	-0.25	-0.34	-0.32
Δd	3.10	3.05	2.25	3.19	2.84	2.70

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